

# New generation EDA tools supporting various MEMS-ASIC integration schemes

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IntelliSense Corporation

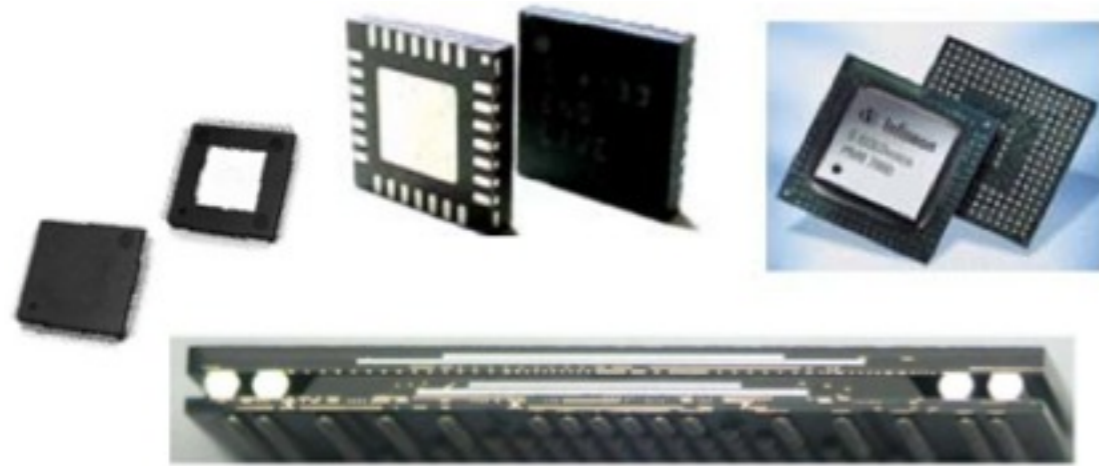
# Outline

- ▶ Introduction
- ▶ Packaging impact on MEMS
- ▶ Challenges in package modeling
- ▶ Case studies
- ▶ Summary

# Introduction

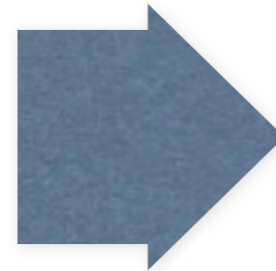
# World of MEMS packaging is evolving rapidly

Learning a new set of TLAs...



## Traditional Packaging

QFP, QFN, POP, MCM, FBGA ...



## Next generation MEMS packaging

3D POP, 3D SIP, 3D WLP, 3D SIC...

## Minimum Package Volume

# Market drivers...



## Form factor

Height & footprint (1mm going down to 0.8 mm)

## Cost

<1 \$ components  $\Rightarrow$  low packaging BOM

## Integration

GPS + Inertial  
BaseBand + Filters  
Antennas + Tuners

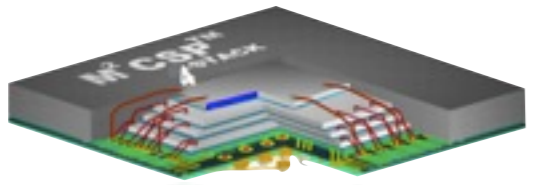
## Environment

Buzzers & bells, extreme temperatures, mechanical flexing, EM issues

## Reliability

Beyond drop tests: Fatigue, vacuum integrity, hysteresis, product year lifetime issues

# Technology drivers...



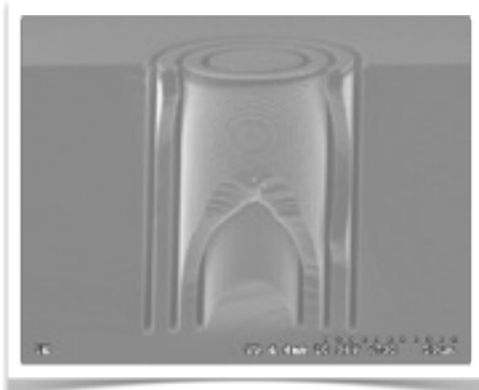
## Chipscale Packaging

Stack large number of dies  
[11 die in 1 mm form factor in 2010  
14 die in 0.8 mm in 2014]



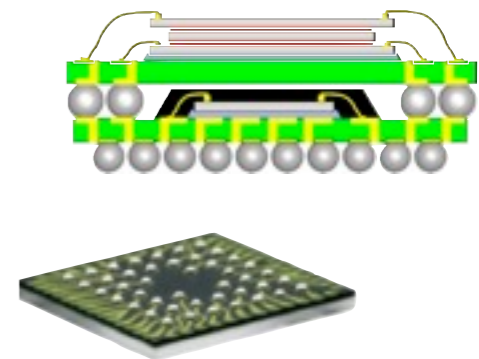
## Die/Wafer Stacking

KGD to KG Sites  
Direct Wafer Stacking  
3D Packaging



## Via Last/Via First/TSV

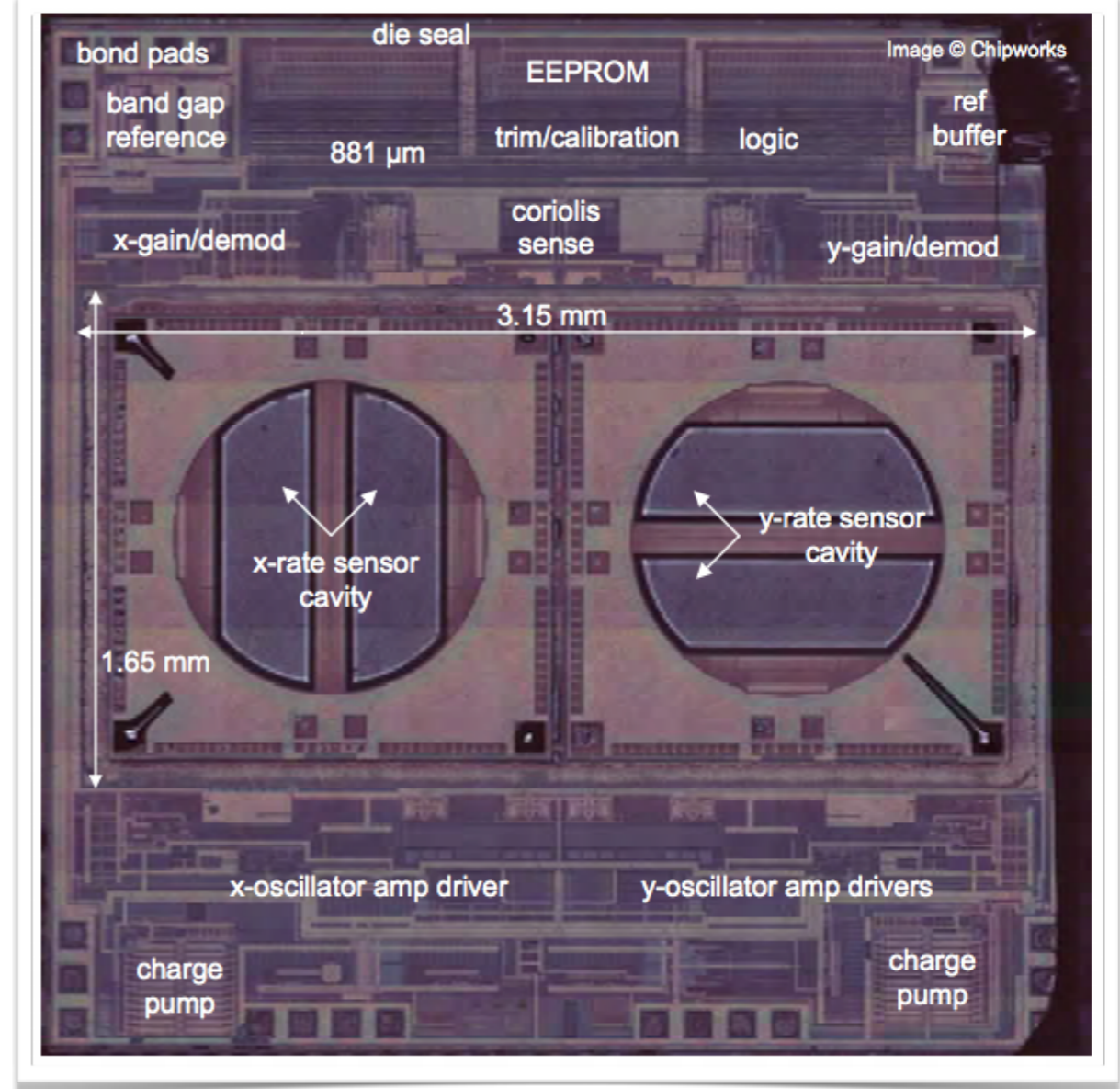
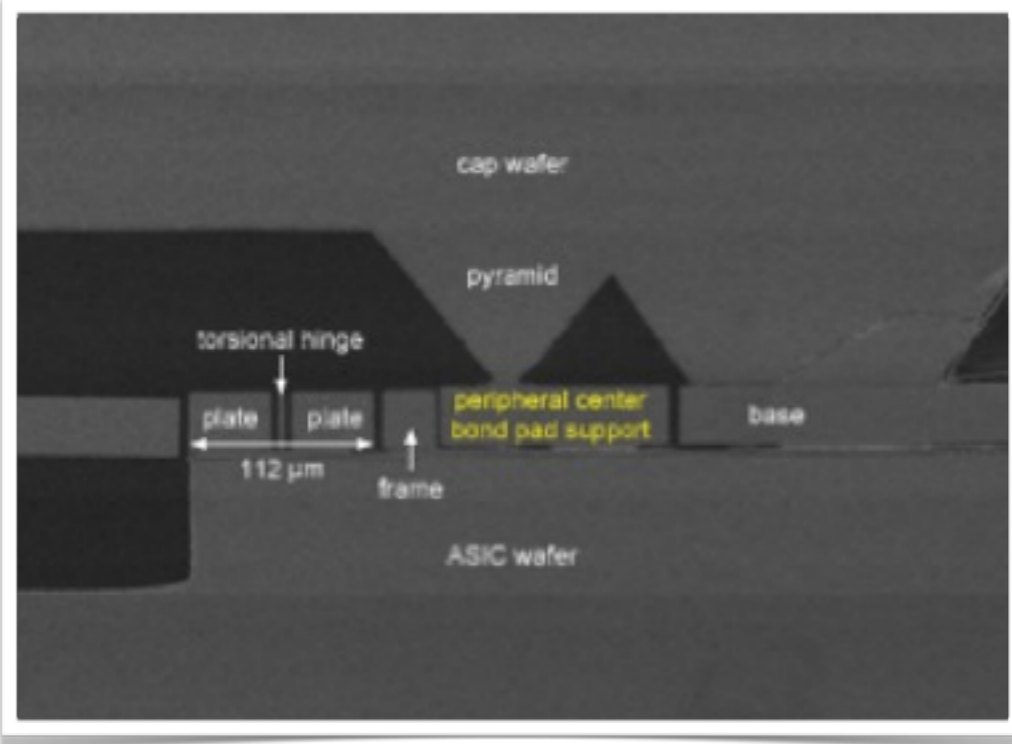
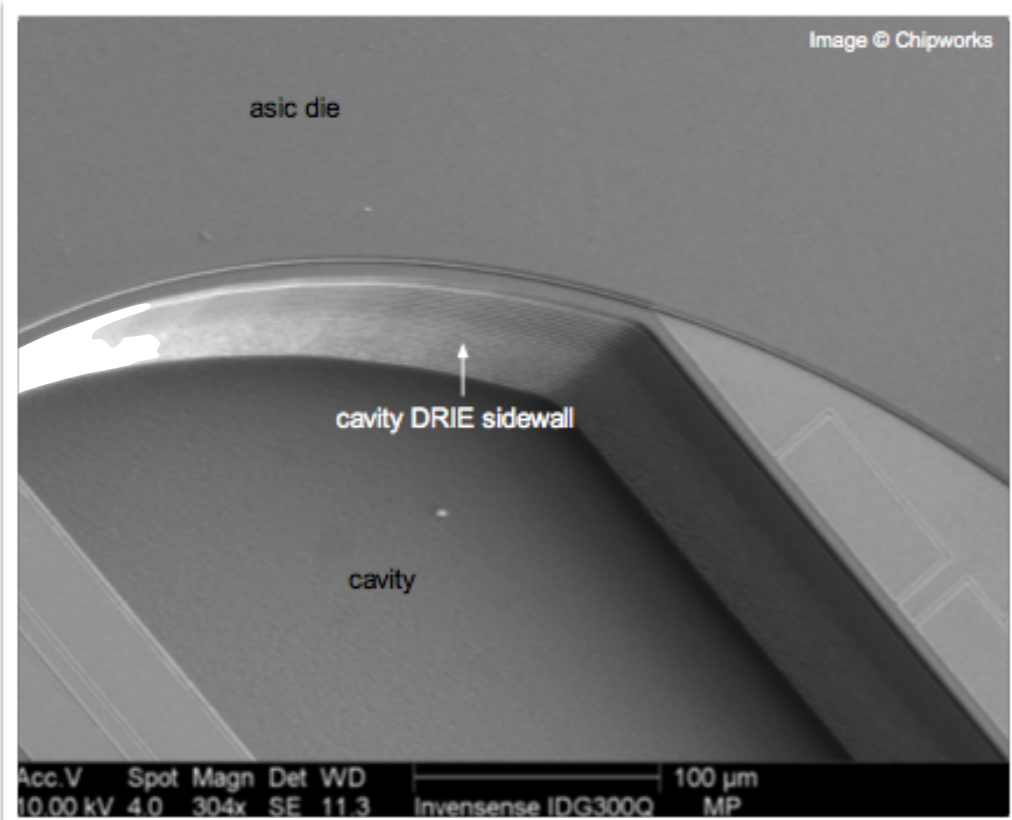
Match KGD to KG sites  
at high throughput



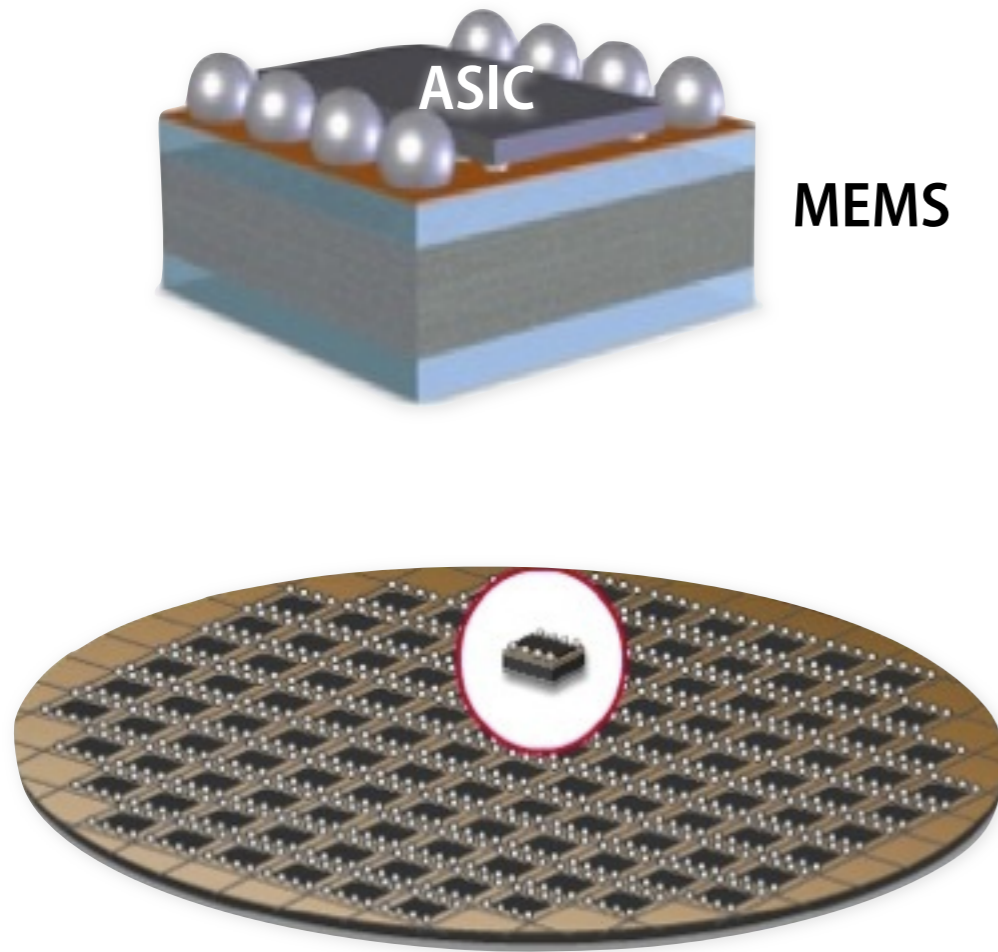
## PoP/eWLP/3DSIC/...

Package on Package  
Embedded approaches

# Invensense gyro: MEMS+ASIC stacking with Al/Ge bonding

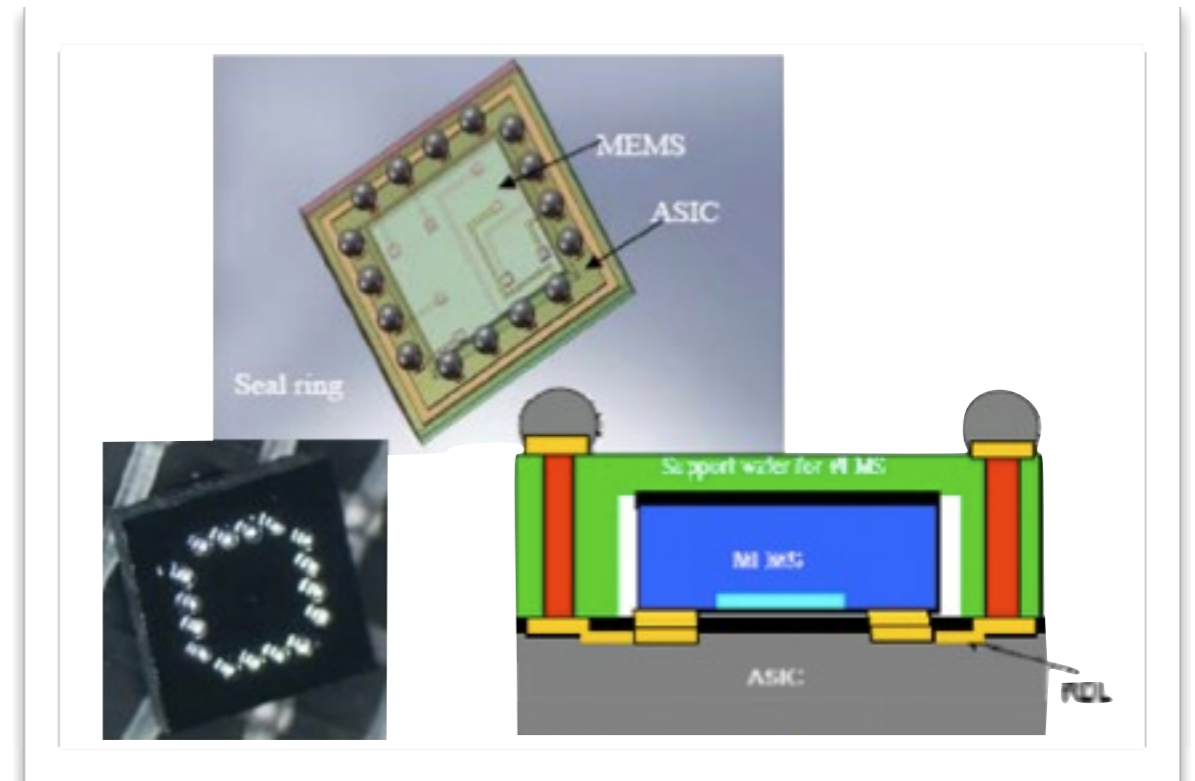


# VTI Accel: Full WLP



**Die on Wafer Assembly**  
**Two level bumping**

# IME (Singapore)



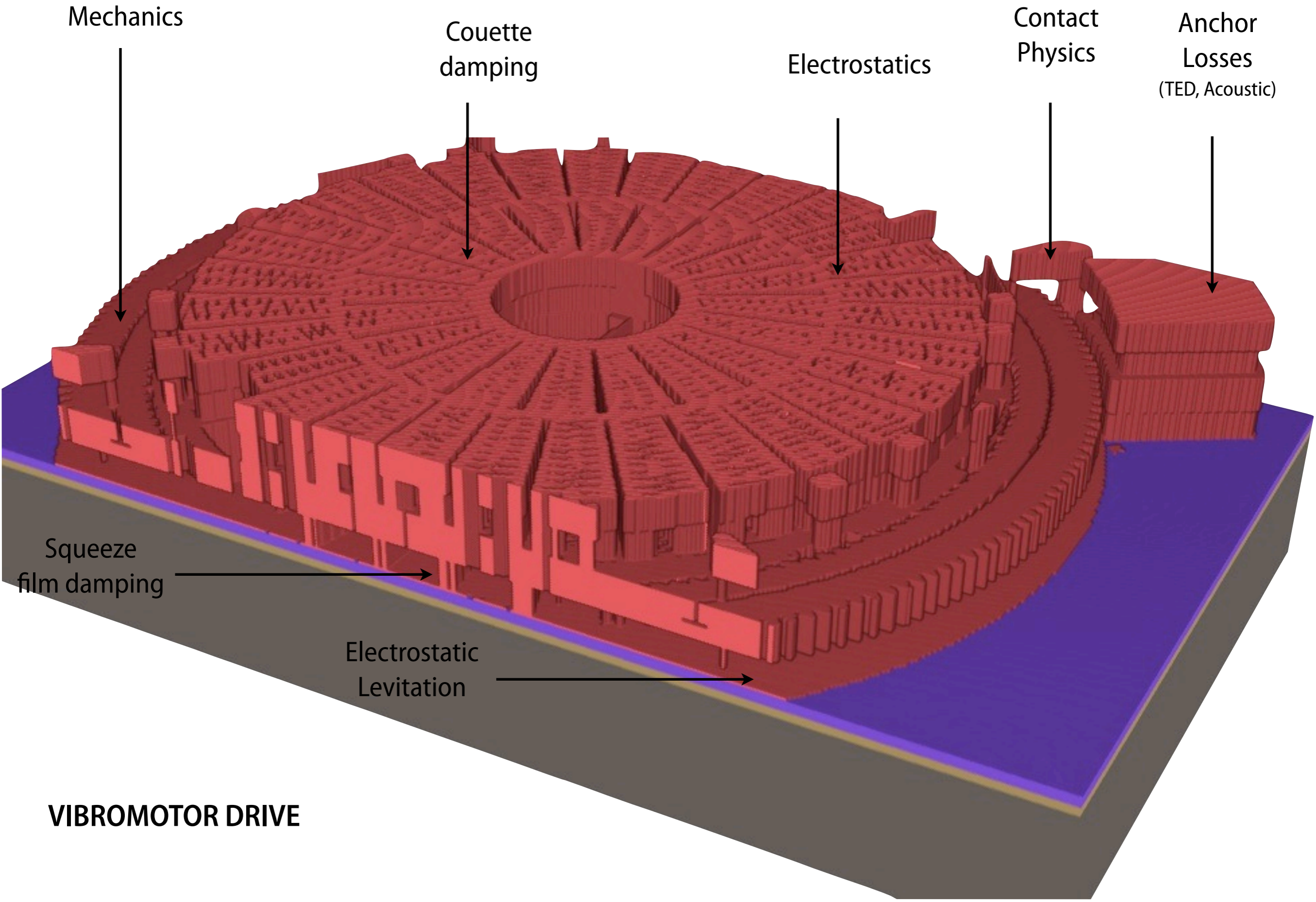
**MEMS ASIC bonding**  
**Support Wafer for MEMS with bumps**



**Increasingly, MEMS is subsuming the package**

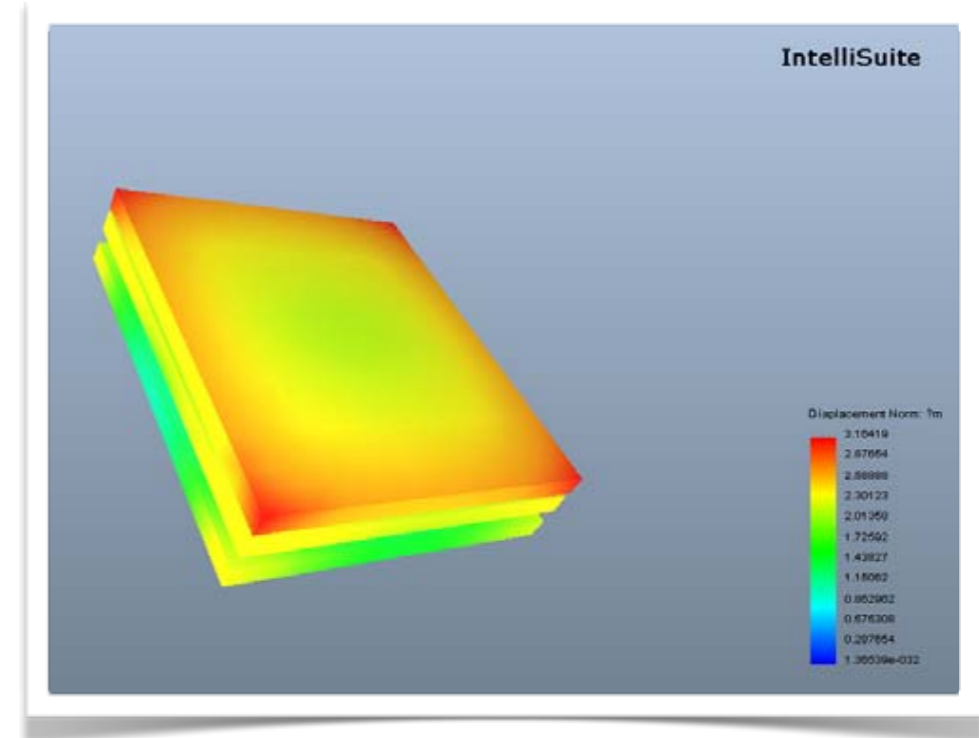
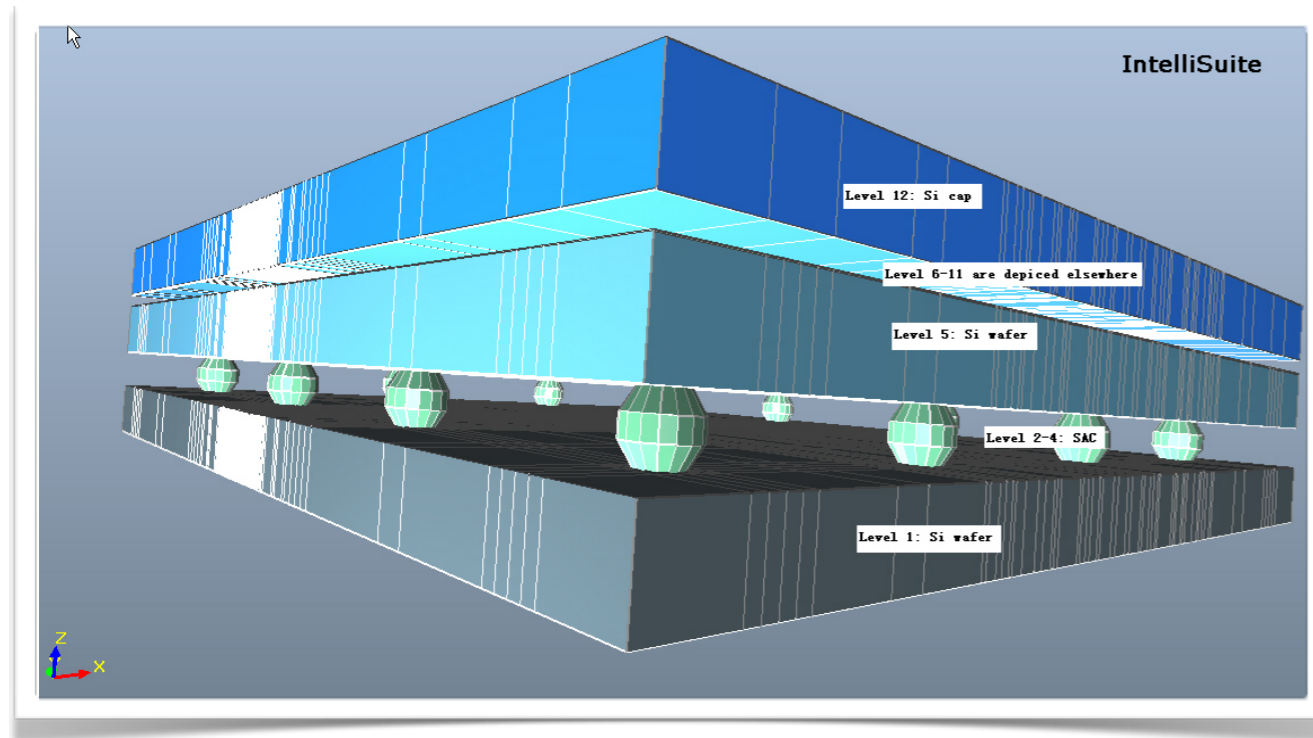
# Packaging impact on MEMS

# A typical MEMS device...



**Now, layer packaging effects on top of this...!**

# Thermo-mechanical



## 3 layer stack:

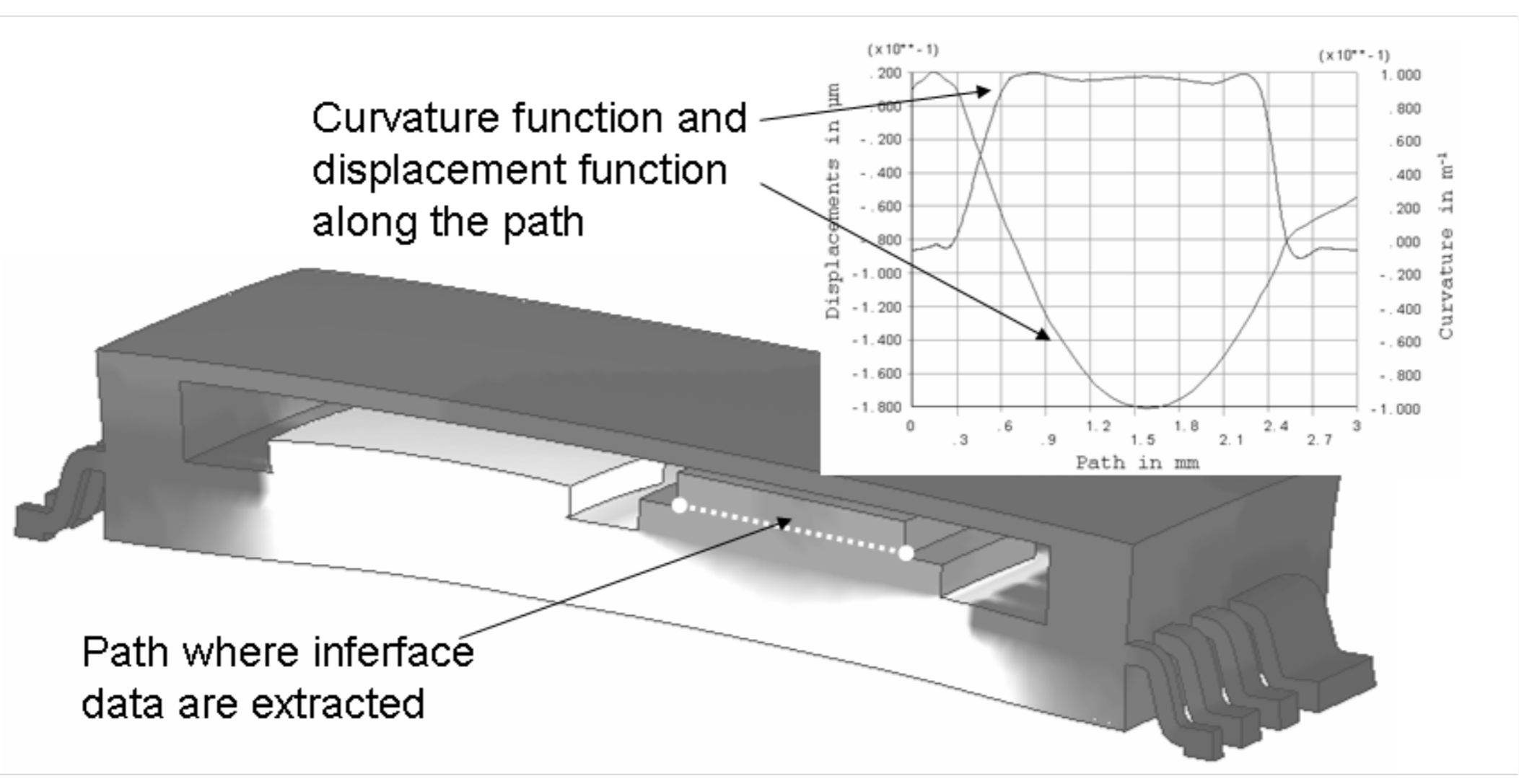
Cap Wafer

Eutectic Bonded to Device Wafer with TSV

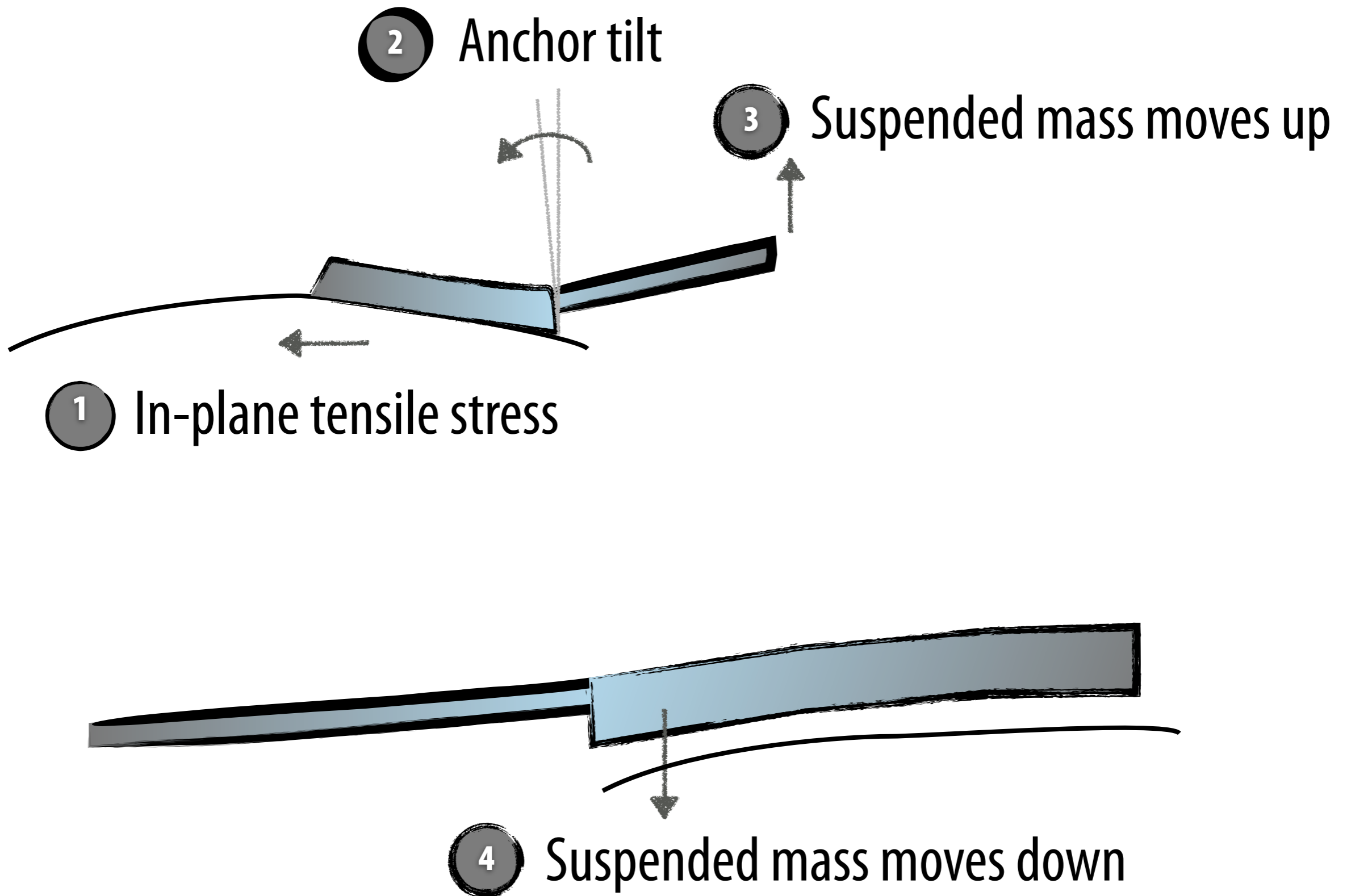
Bumped to ASIC wafer

(underfill not shown)

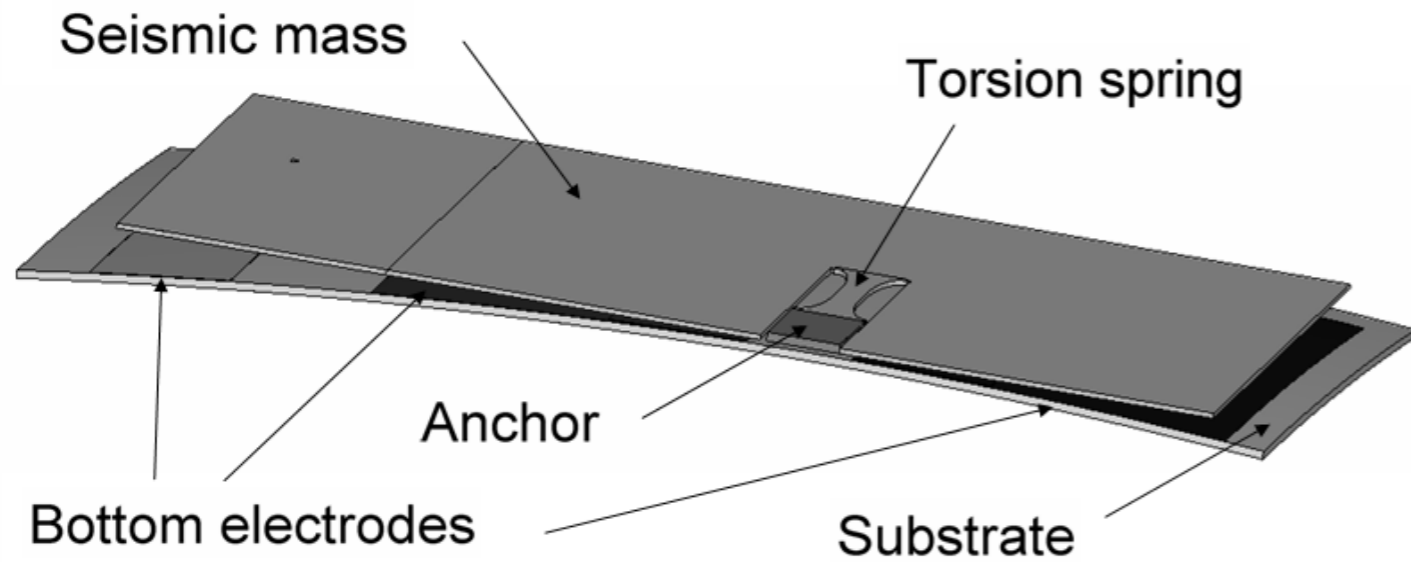
# Thermo-mechanical



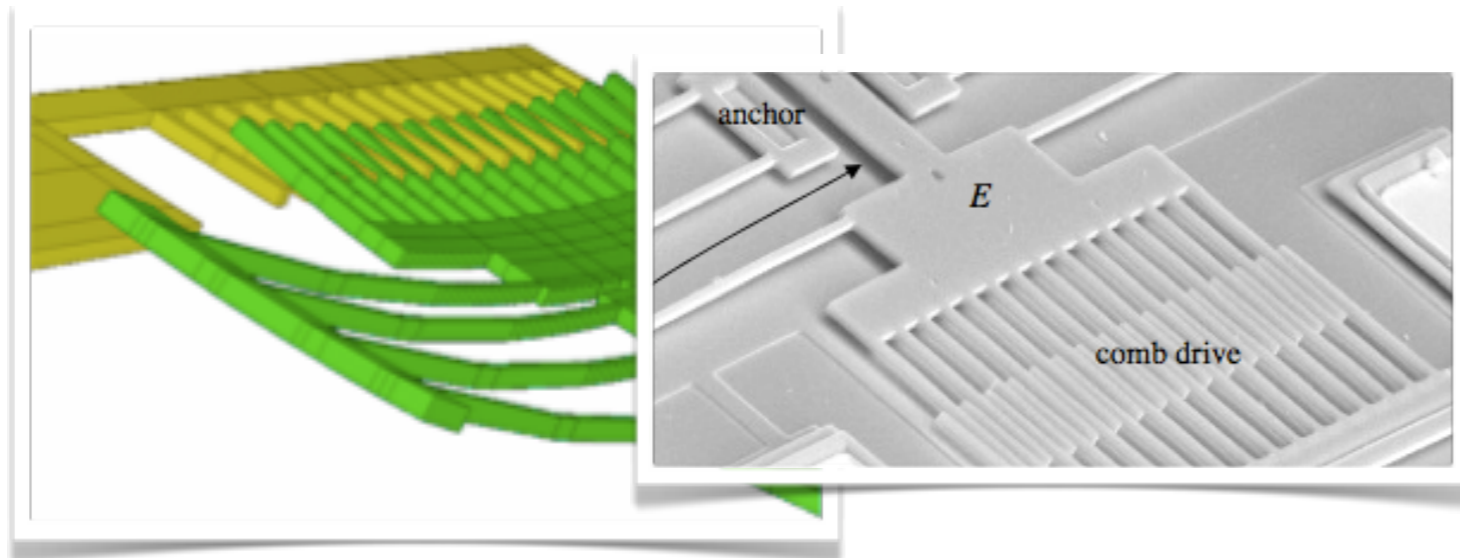
# Thermo-mechanical



# Electro-thermal



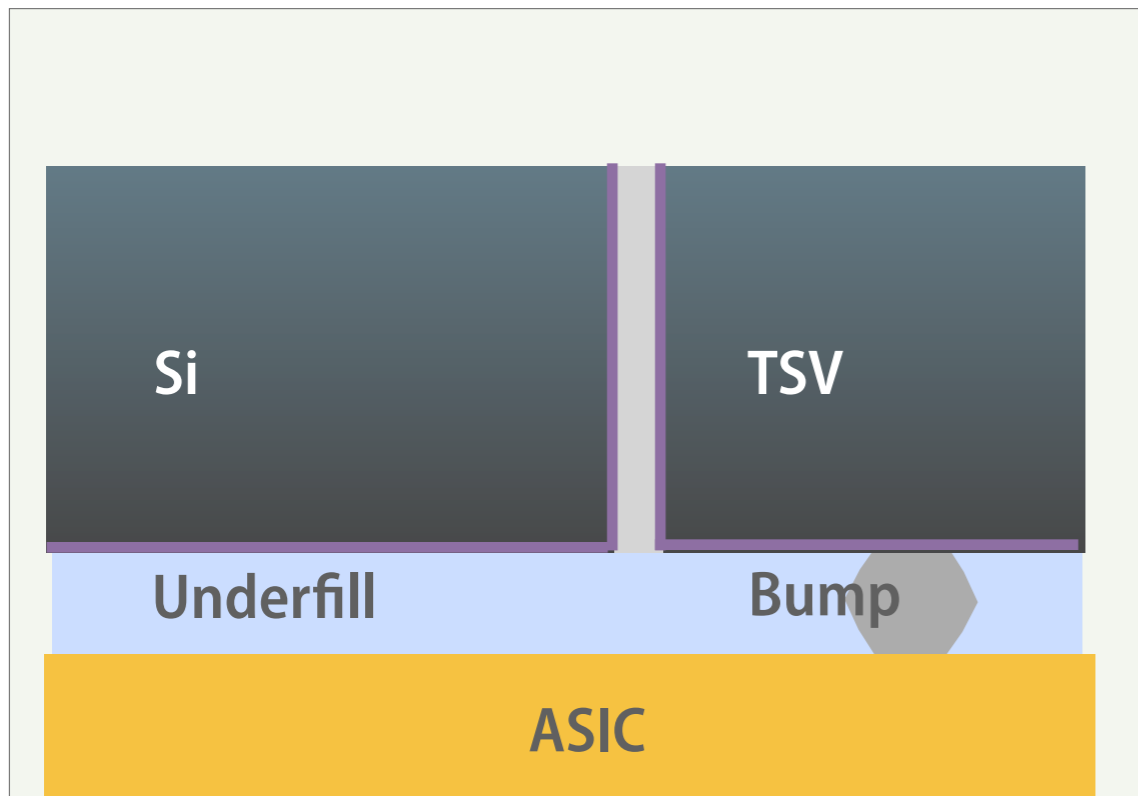
**Bottom Electrodes**  
**Temperature sensitivity due to curvature**



**Comb Electrodes**  
**Curvature related sensitivity**

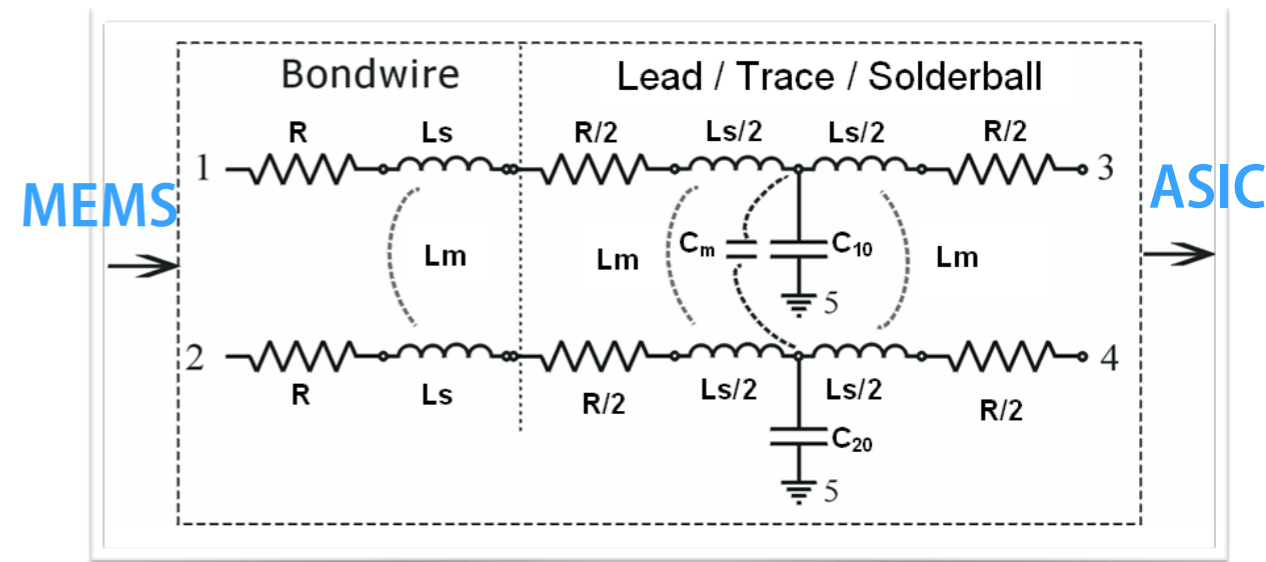
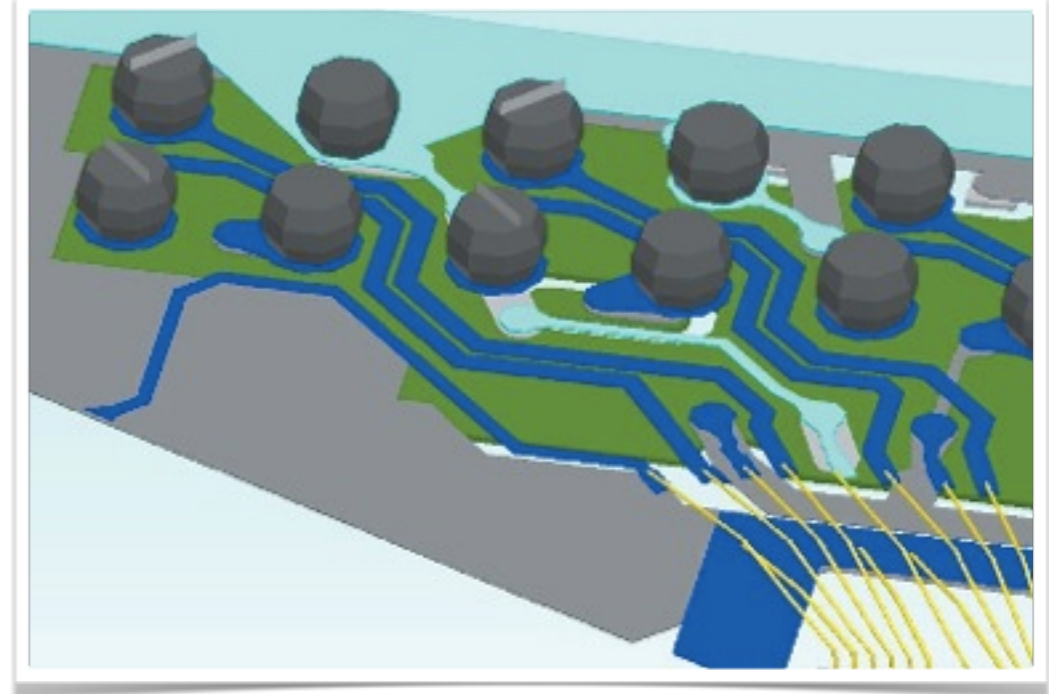


# Electrical



Underfill dielectric increases  
shunt capacitance  $\Rightarrow$  decreased sensitivity

Shunt issues



Parasitics & cross talk

# Packaging impact...

Mechanical                      Mechanical parameters: stresses, spring constants, damping, shock

Electrical                      Sense & shunt capacitance change; pull-in and tuning voltage change

Thermal                      Temperature co-efficients, temperature gradient co-efficients

Ambient                      Vacuum change, viscosity change in air, moisture effects

Electromagnetic              Parasitic capacitances, inductances and resistance



Manifests as bias stability, temperature coefficients, and other performance killers...

# Challenges in package modeling

**MEMS Design Is A Collaboration Challenge...**



Program Manager



System Architect



Device Engineer



Process Engineer

*THE CHAIN OF PAIN...*



Manufacturing Engineer



Test Engineer




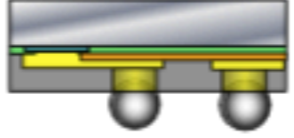




Packaging Engineer

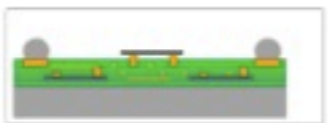
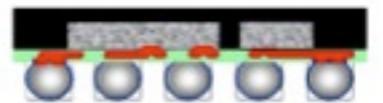
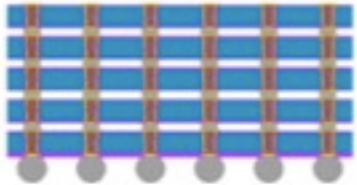
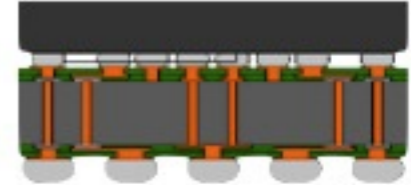


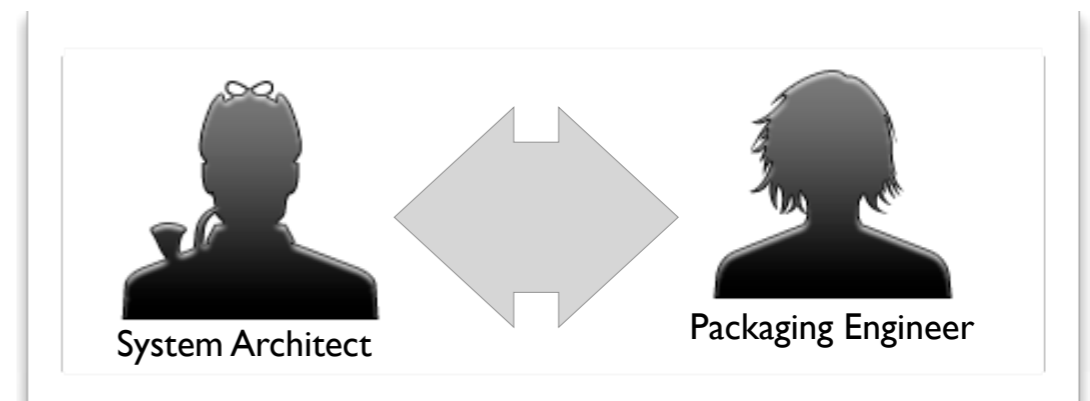
Electrical Engineer

# The chain of pain... (1)

How do you explore a huge range of packaging options?

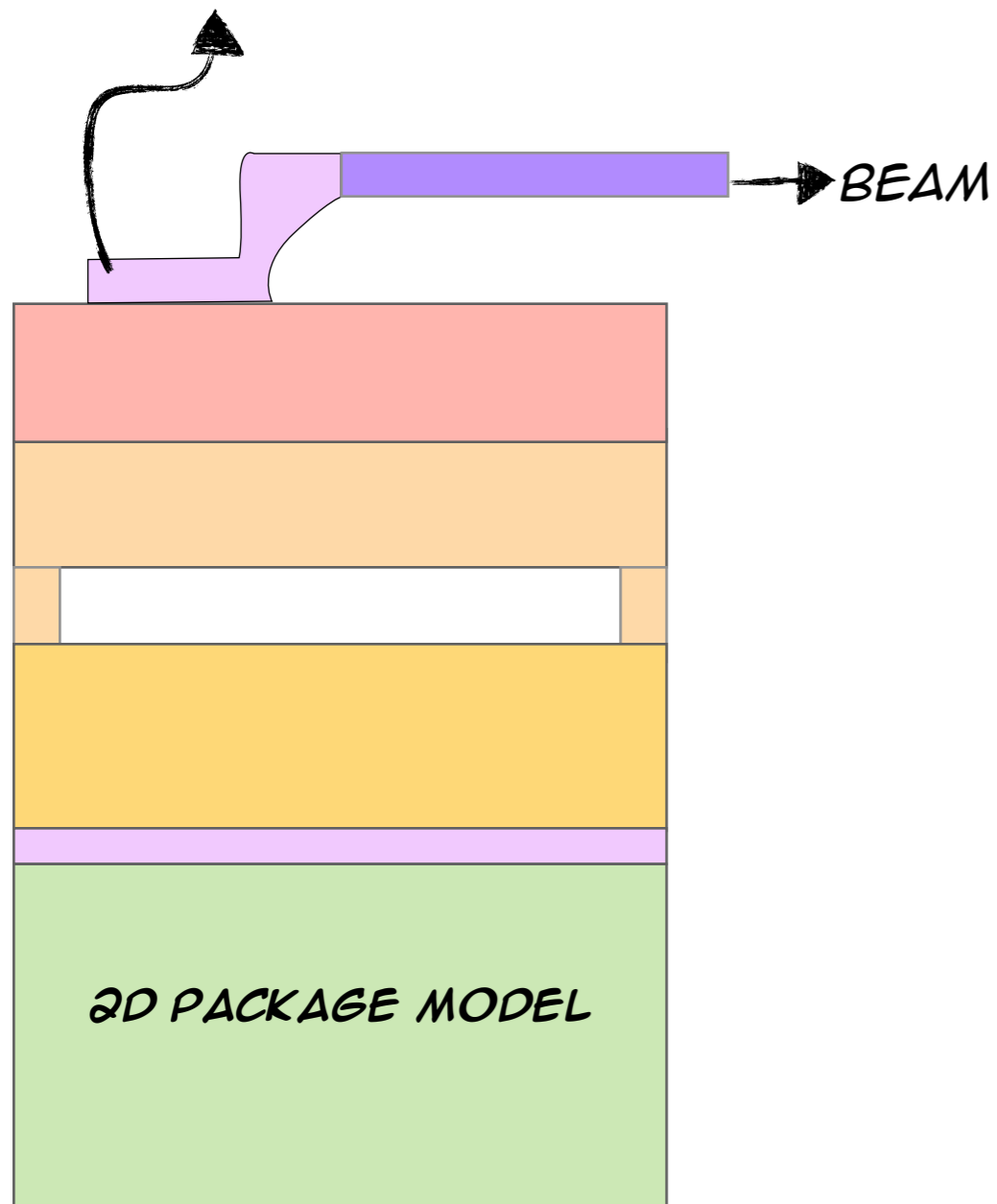
	
Wafer level CSP in the simplest structure	Wafer level CSP with copper post and resin mold
	
Opto wafer level CSP with tapered TSV interconnection	Opto wafer level CSP with beam lead metallurgy
	
IPD embedded silicon substrate	Build-up substrate through wafer level fabrication

	
Thin Chip Integration (Embedded device in polymer dielectric)	embedded Wafer Level Ball Grid Array
	
Stacked devices with Through Silicon Via's (TSV)	Via Last + Stacking

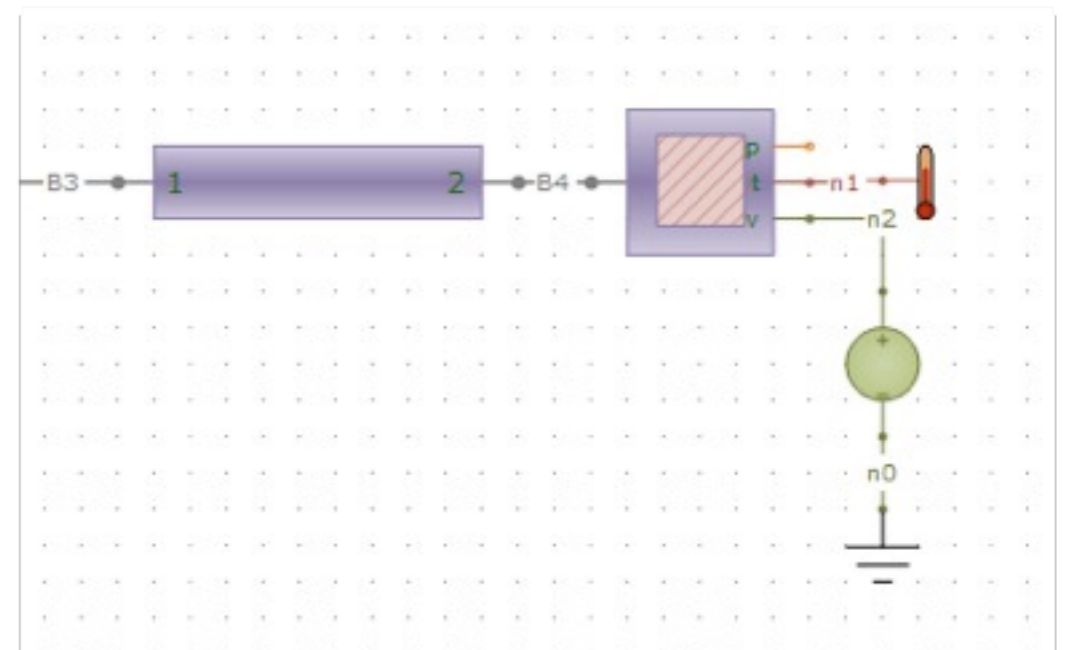
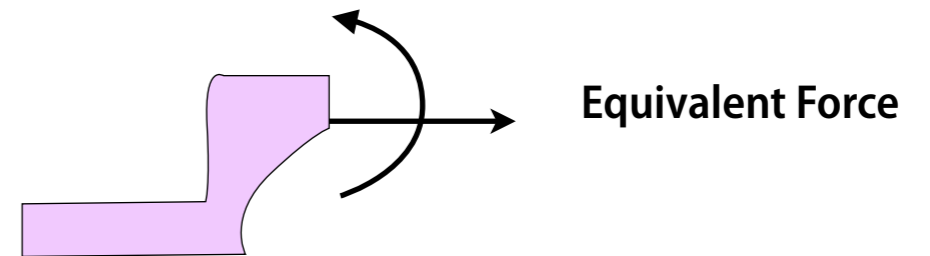


# Compact models for packaging...

*STRESSED ANCHOR MODEL*



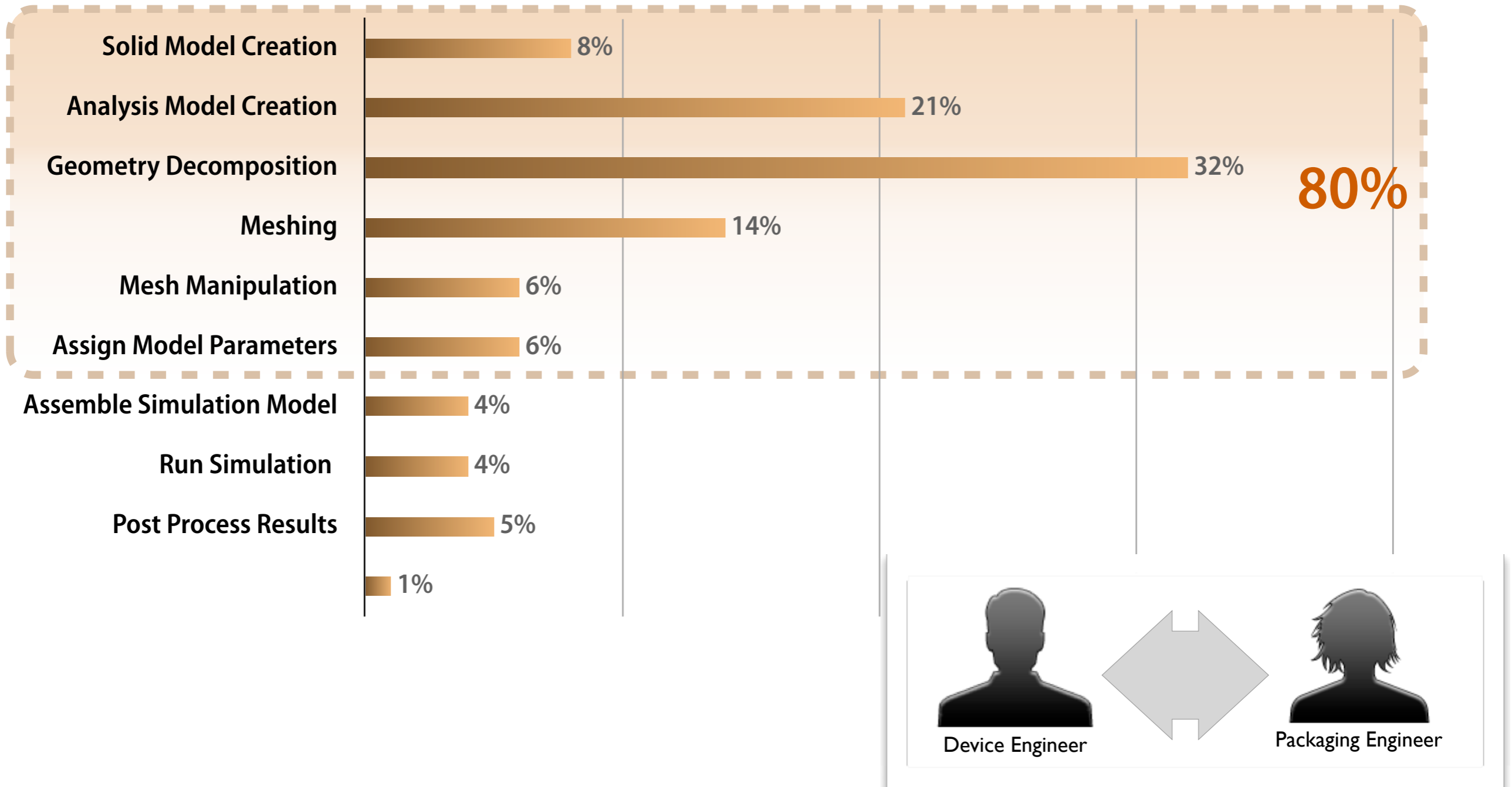
Equivalent Moment



# The chain of pain... (2)

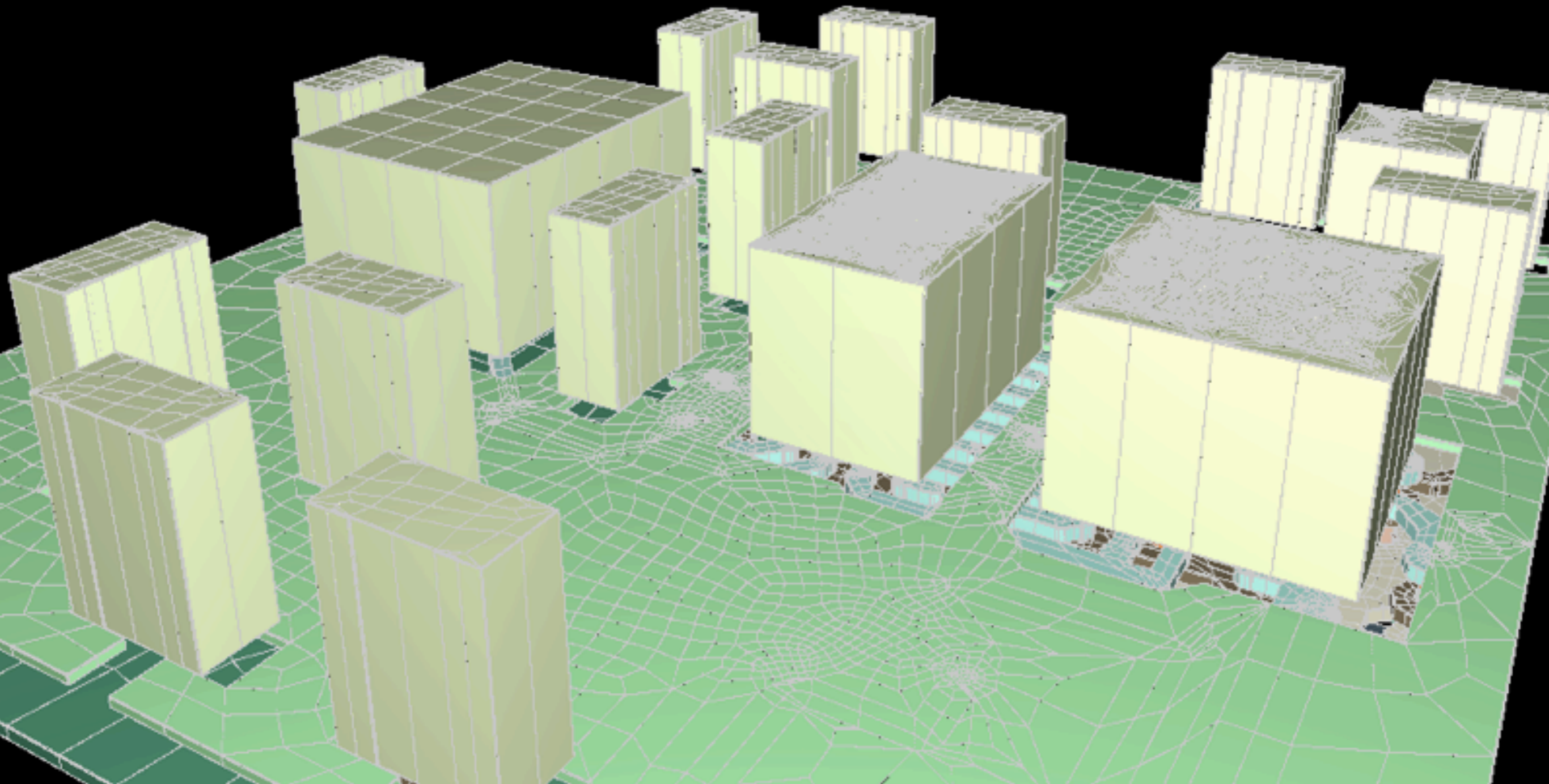
How do you efficiently create MEMS + Package models?

Close to 80% of the time spent in mesh creation and manipulation...

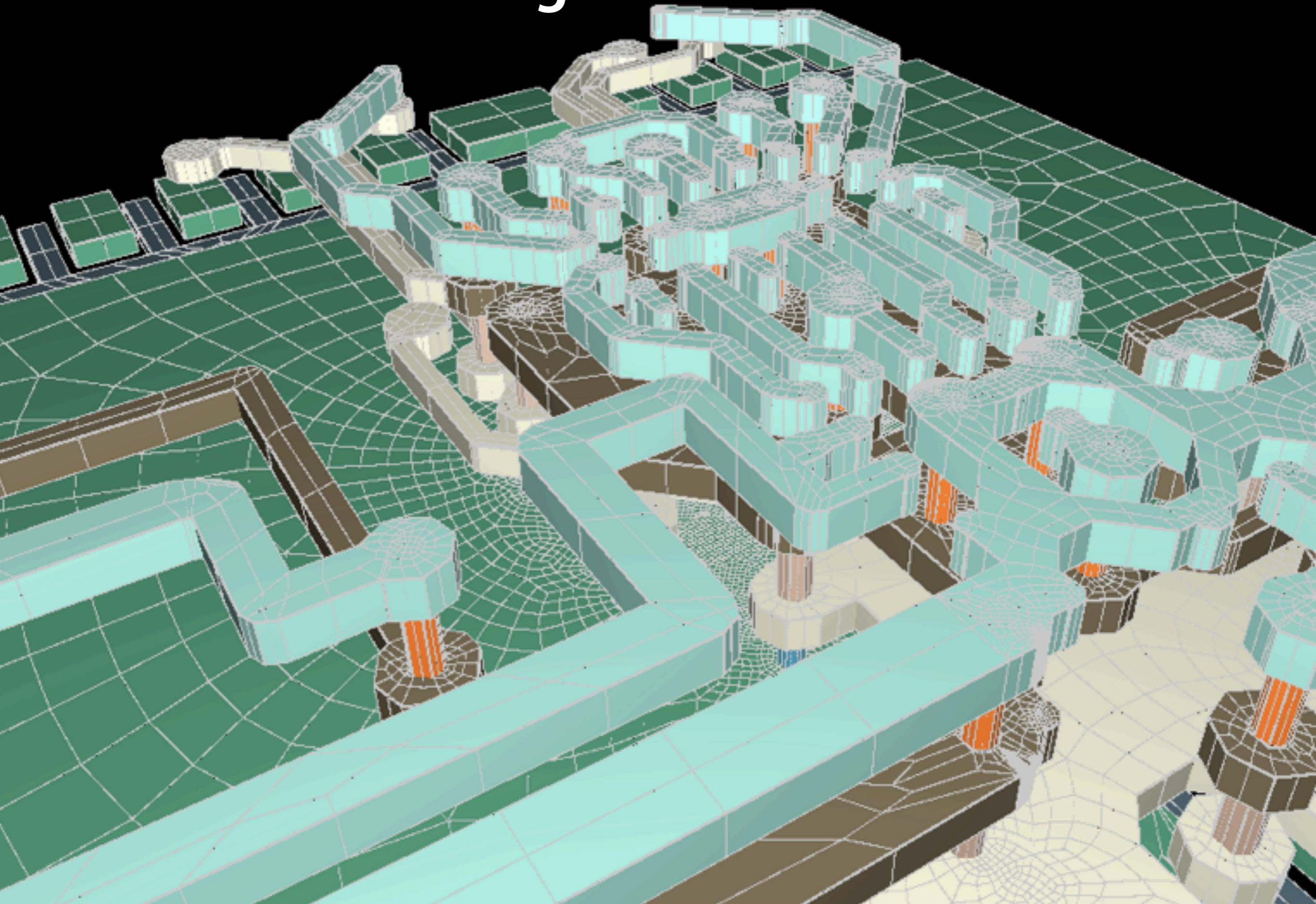




# Automated HEX meshing...



# 1 Click Hex Meshing...

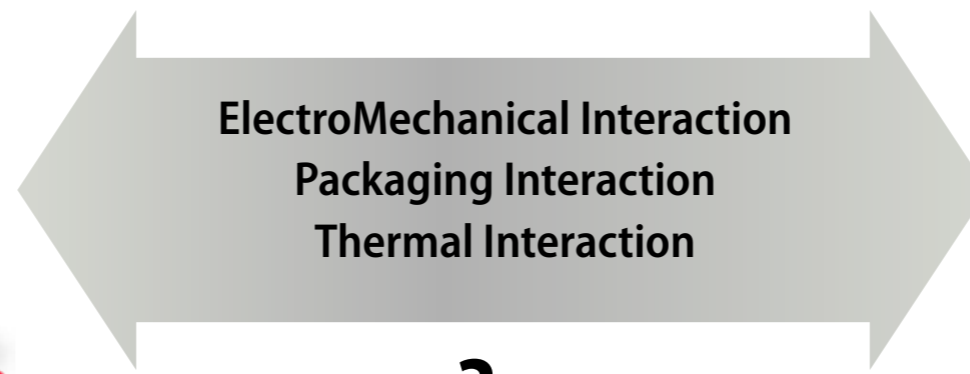


# The chain of pain... (3)

How do you compensate packaging and temperature effects?



**MEMS+Package**



?



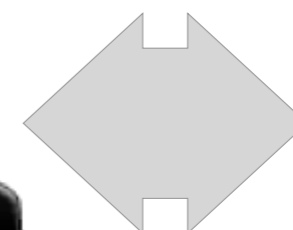
**ASIC**



Packaging Engineer



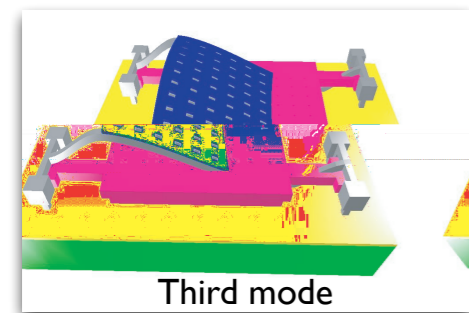
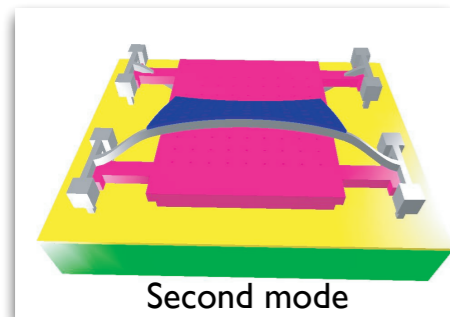
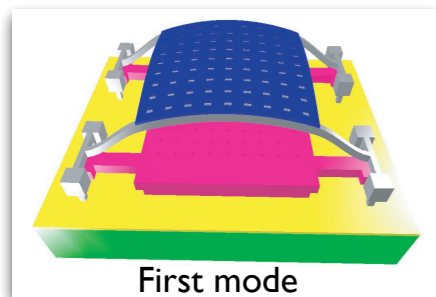
Device Engineer



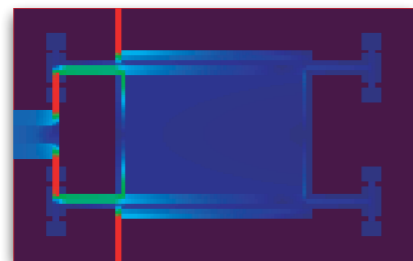
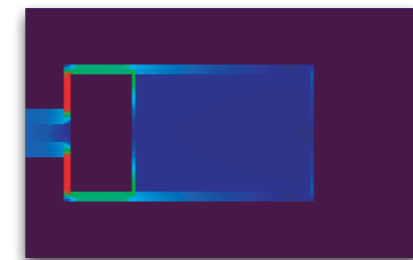
Electrical Engineer

# Automated System Model Extraction (SME)

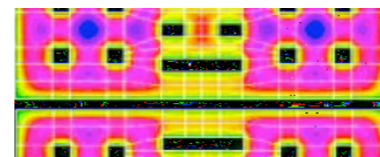
Capture strain energy associated with each mode



Capture electrostatic energy associated with each mode



Capture fluid damping characteristics



Arnoldi/Krylov sub-space reduction



N-DOF behavioral model based on Lagrangian formulation

$$\frac{d}{dt} \left( \frac{\partial L}{\partial \dot{q}_j} \right) - \frac{\partial L}{\partial q_j} = 0$$



Compact Representation

**HDL**

Hardware Description

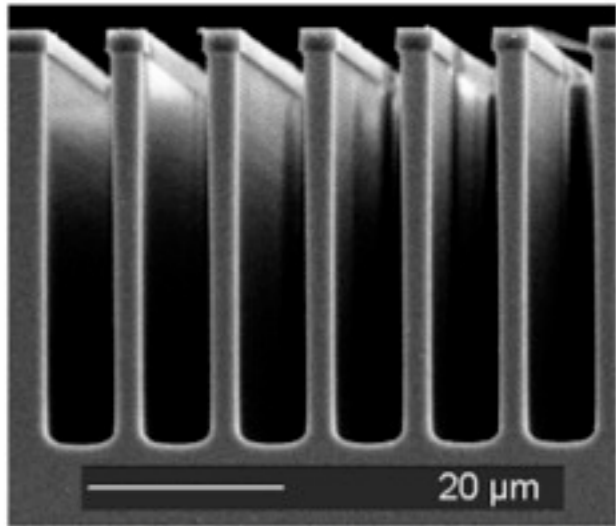
① Capture total energy of relevant mode (Mechanical, Electrostatic, Dissipation)

② Krylov/Arnoldi methods to generate Lagrangian formulation

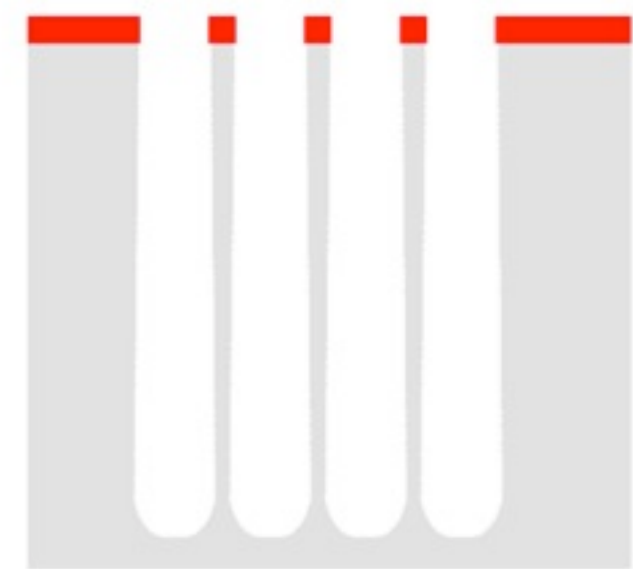
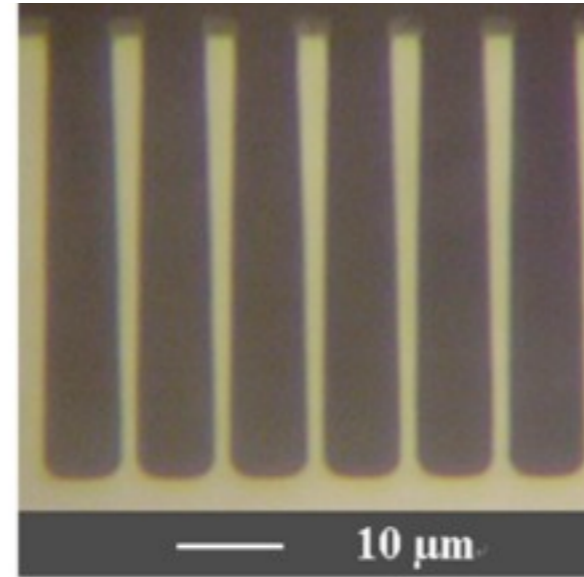
③ Create Compact model for system modeling

# The chain of pain... (4)

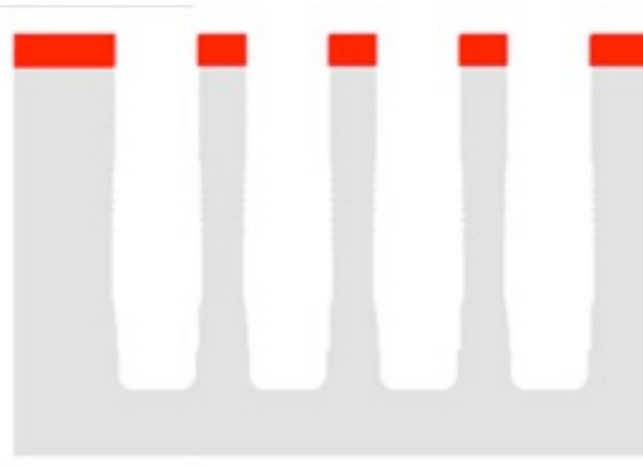
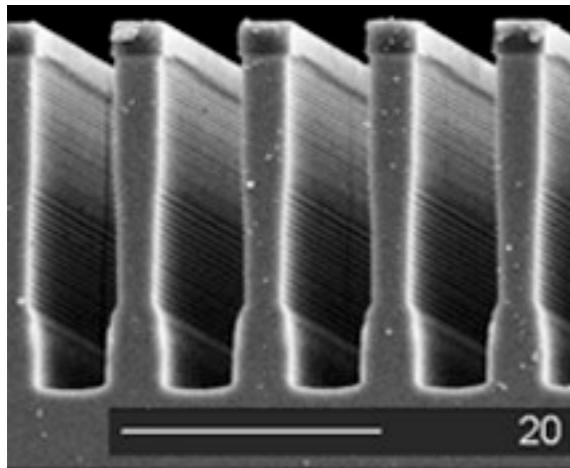
How do you fine tune TSV processes?



The experimental results of the etching. Comparison of etching 5 μm openings with an etch/dep cycle of 7s/7s.



Comparison of etching a 5 μm trench with a 7s/8s cycle



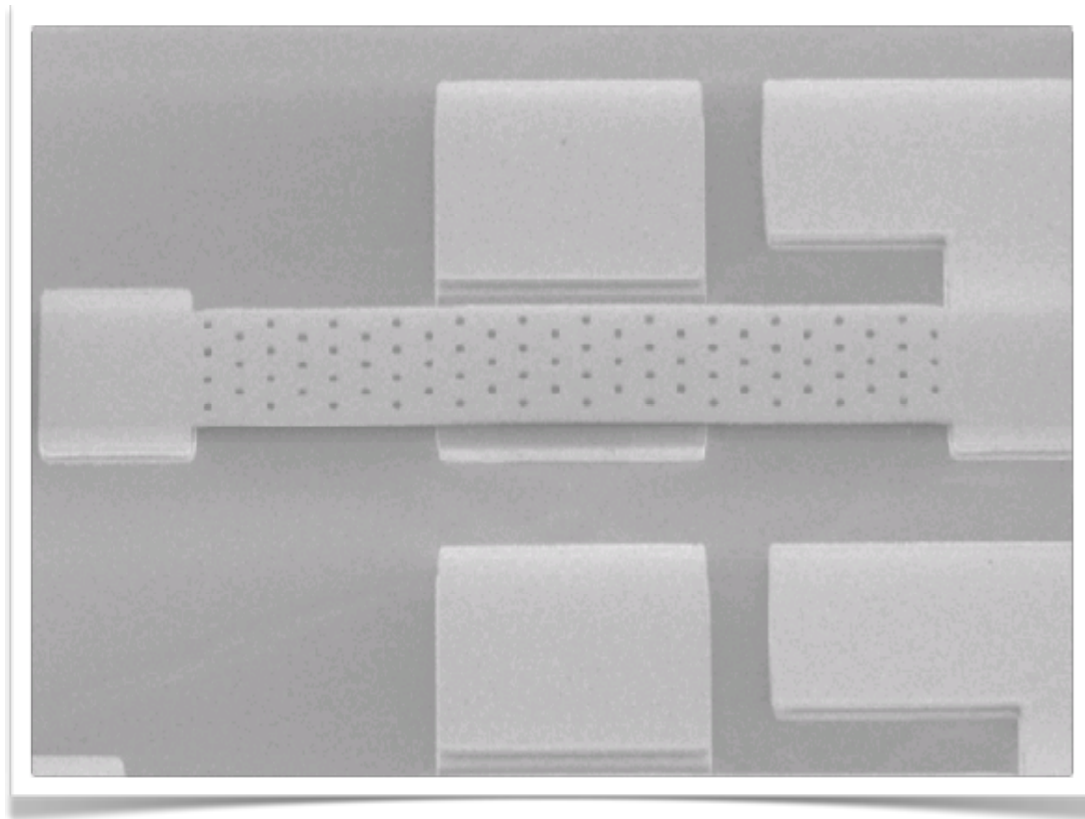
The experimental result of the etching of trenches using three etching steps with different etching/polymerization time configurations. 7s/7s, 9s/7s and 5s/7s are used sequentially, each for 5 minutes.



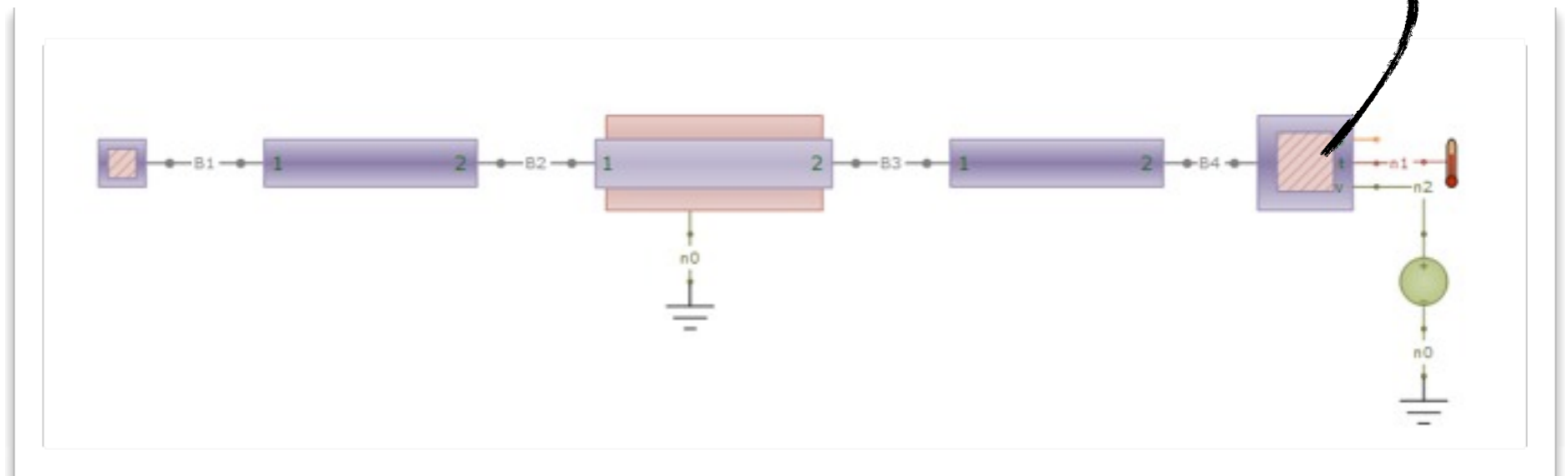
Process Engineer

# Case Studies

# Northrup: RF Switch

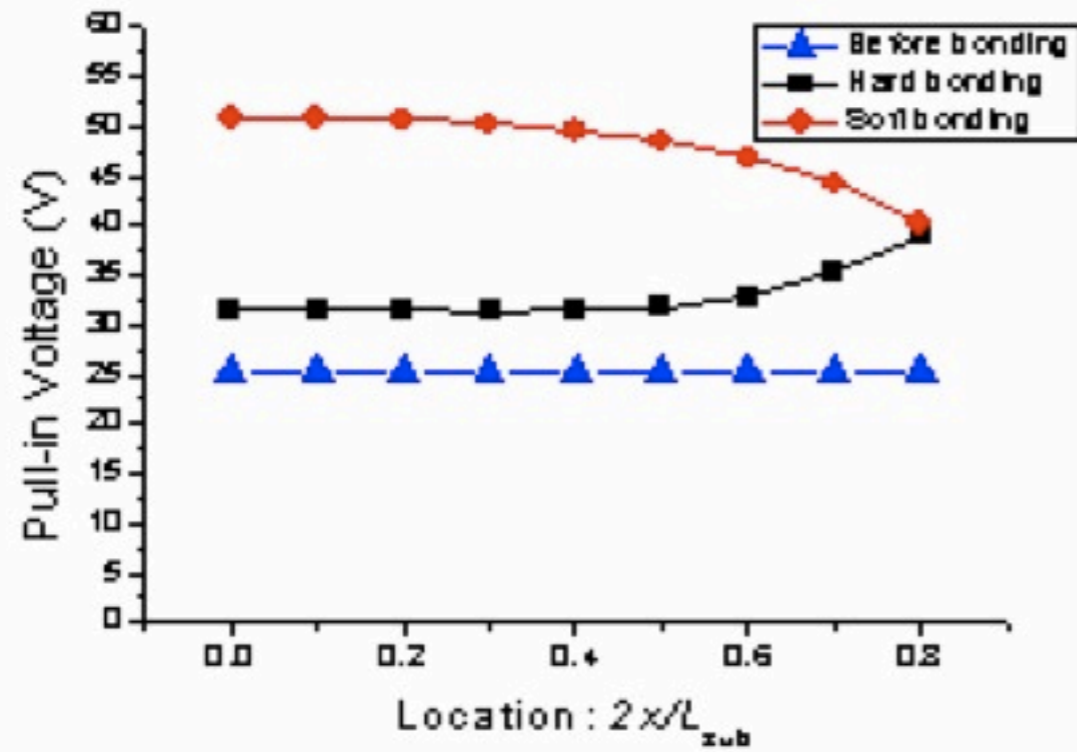


Stressed Anchor Model

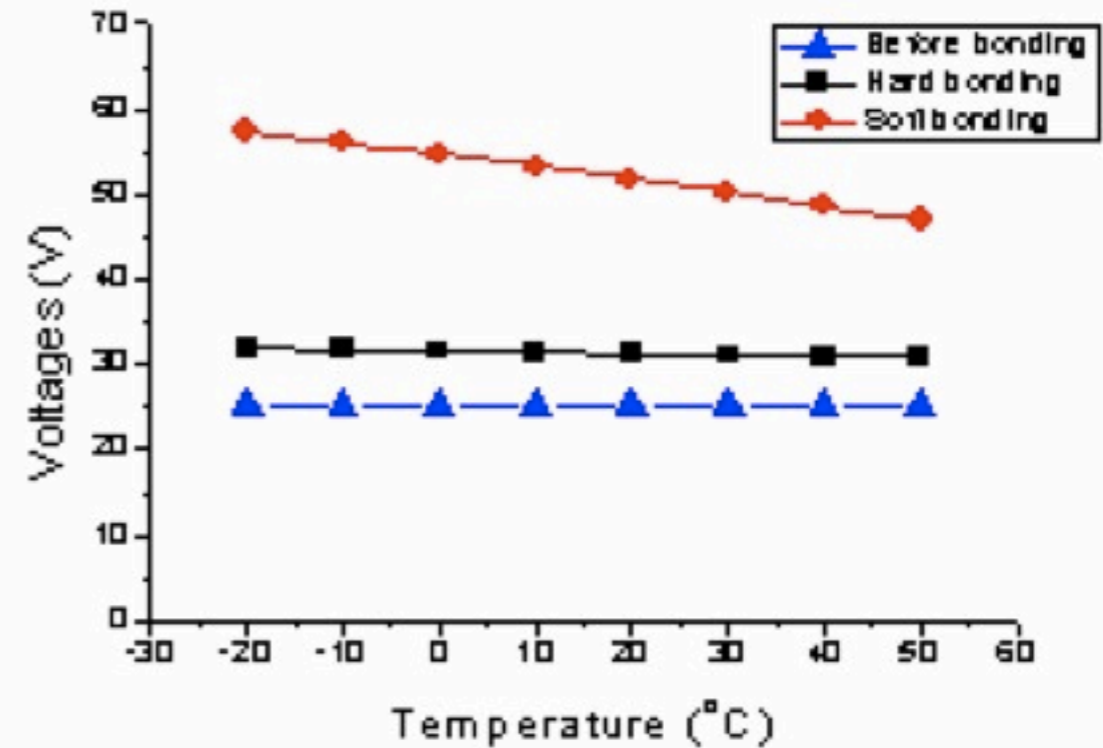


# RF Switch

Within 10% of full FEA models...



(a)



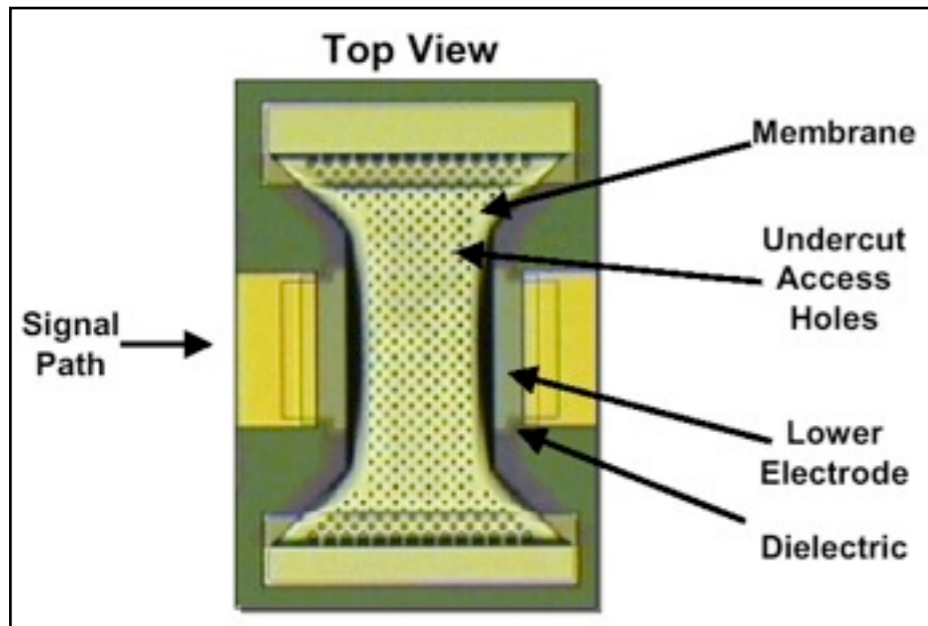
(b)

**Hard bonding:** Au-Si Eutectic on Ceramic Substrate

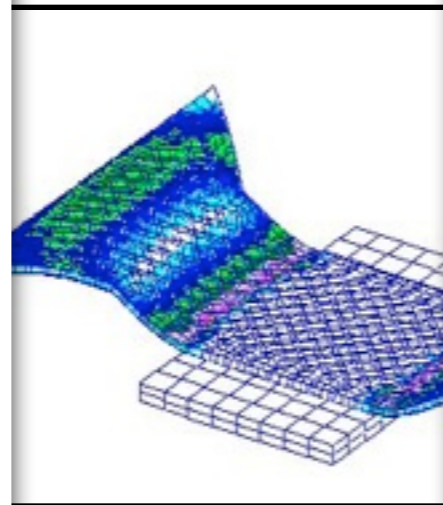
**Soft bonding:** Epoxy bonding on FR-4



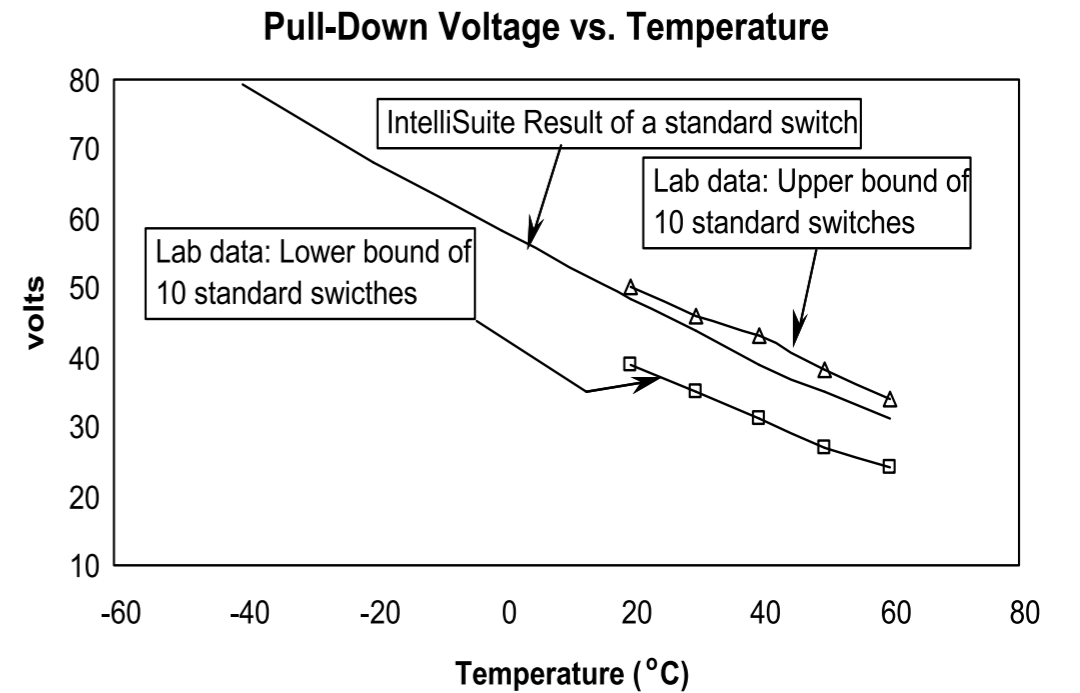
# Raytheon RF Switch



SEM AND DEVICE CONFIGURATION

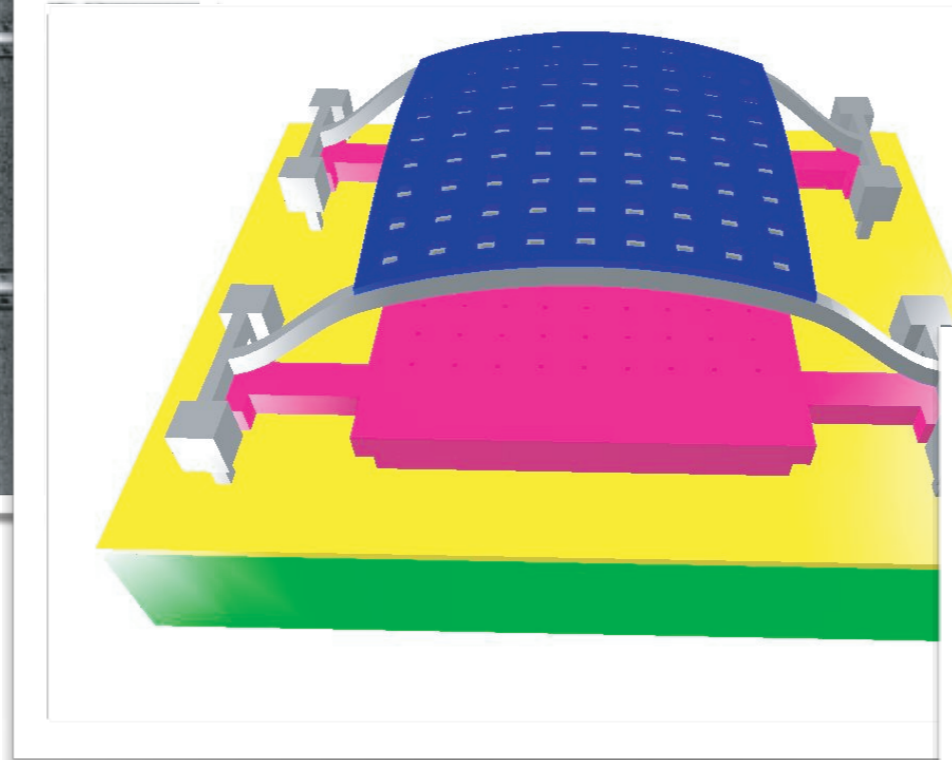
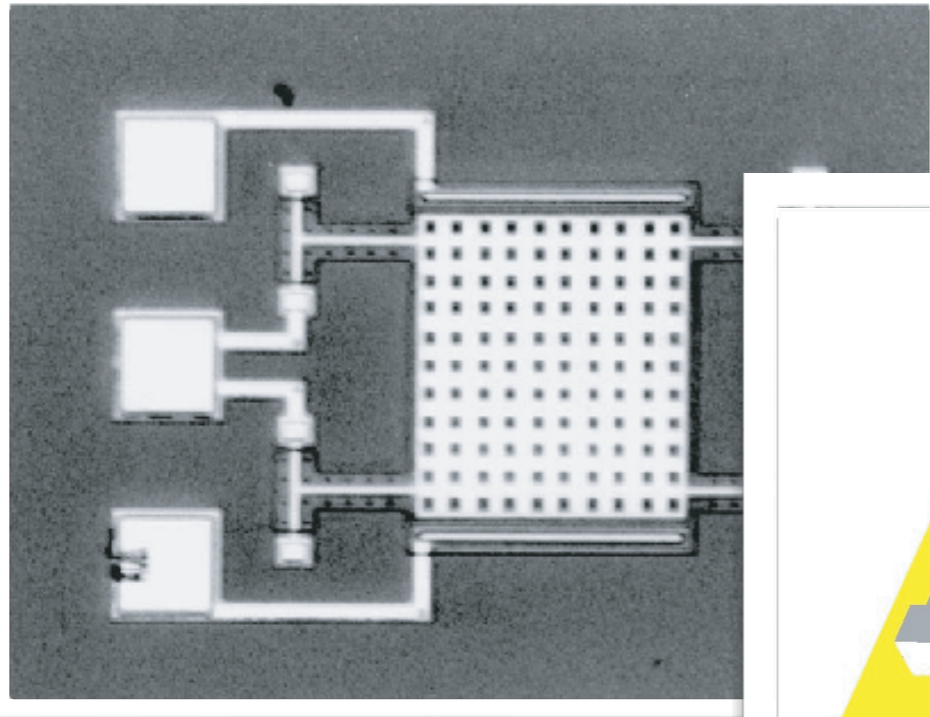


CONTACT ANALYSIS VON M

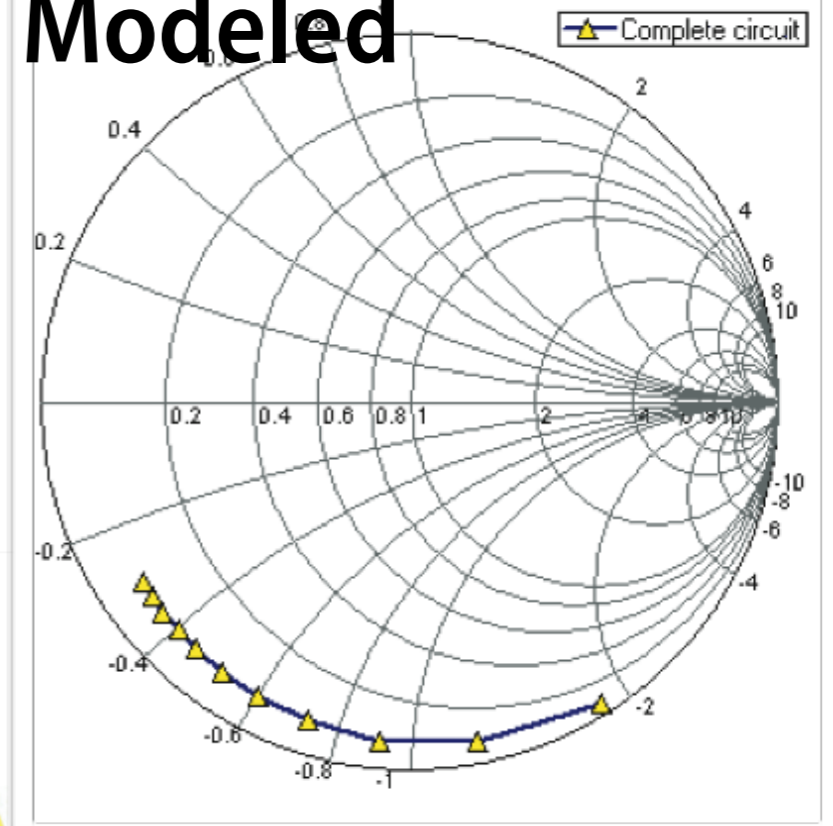


PERFORMANCE OF SWITCH

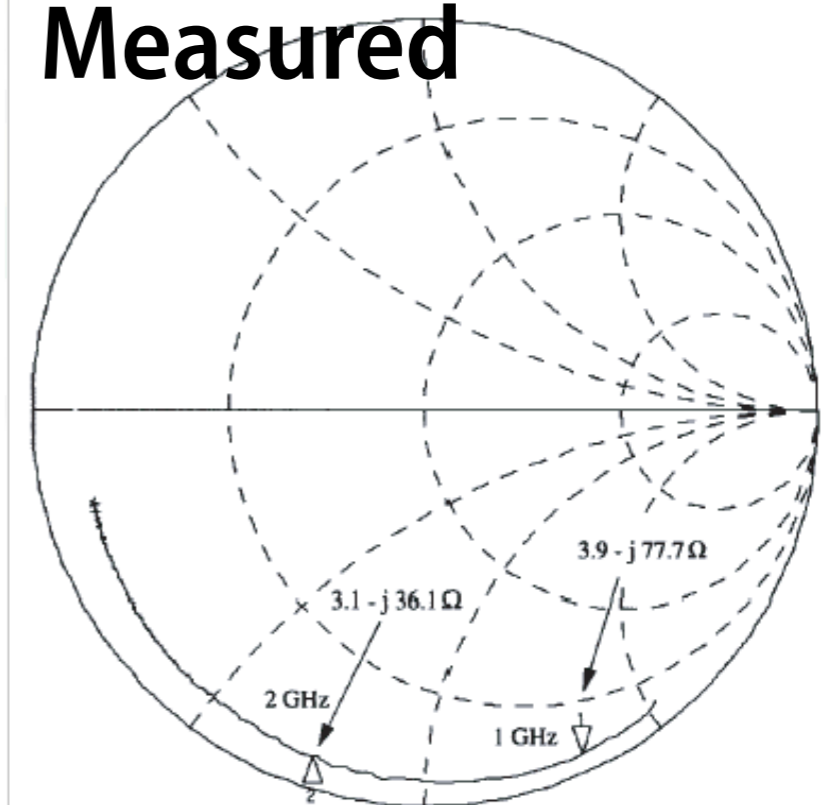
# Tunable capacitor



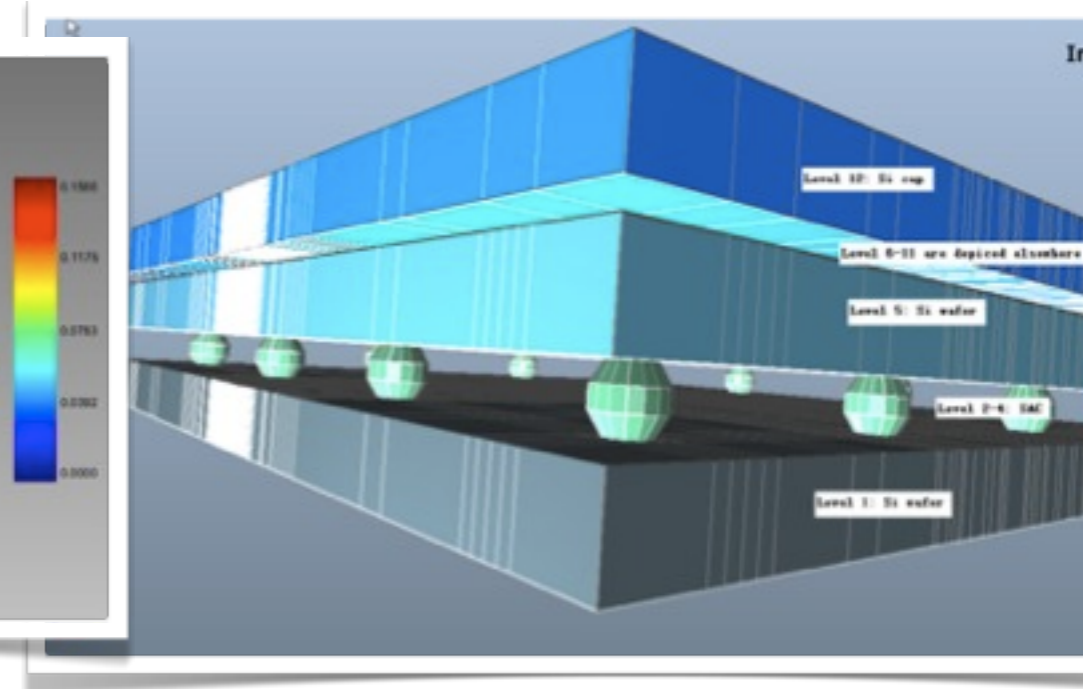
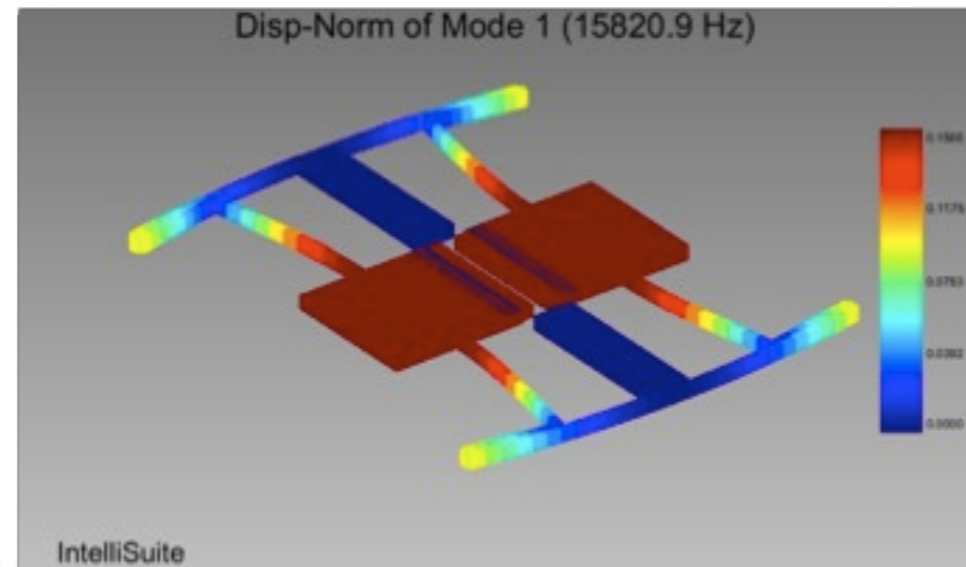
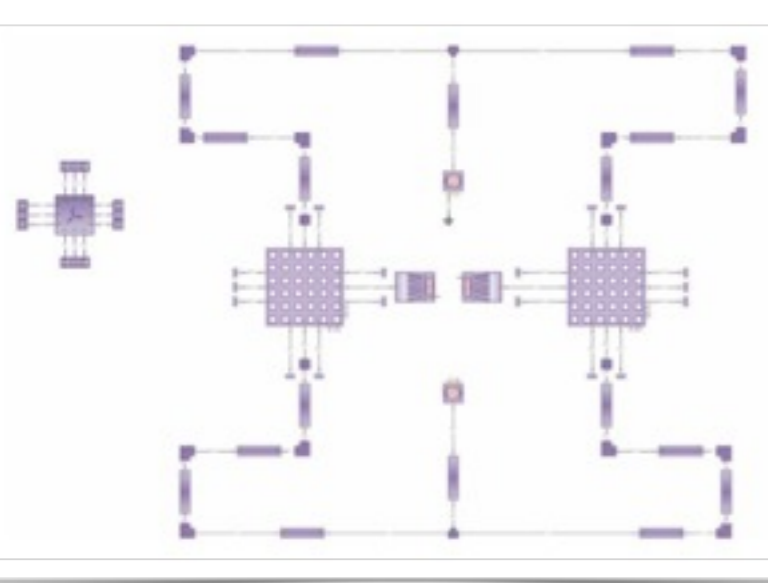
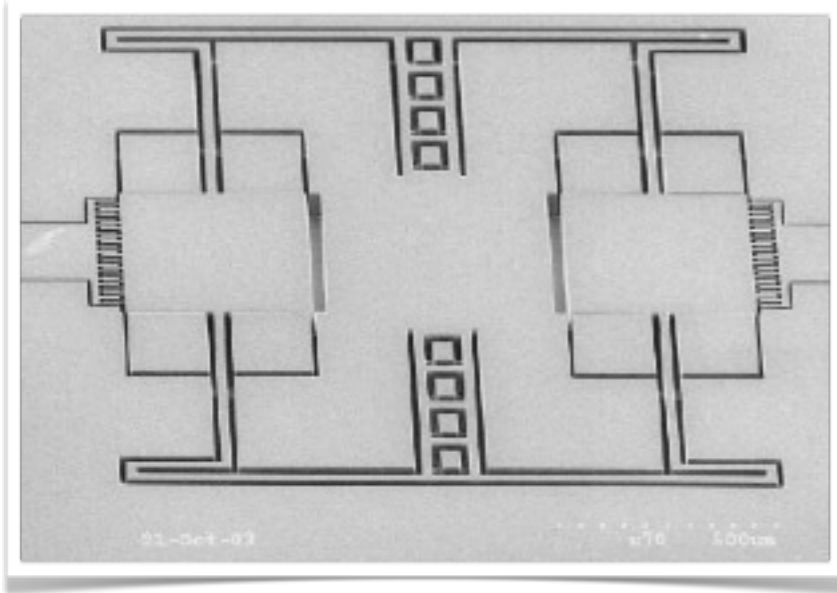
## Modeled



## Measured



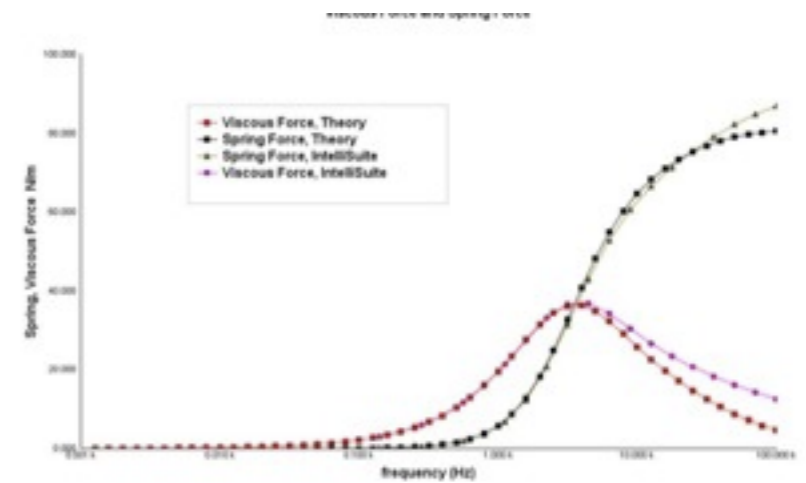
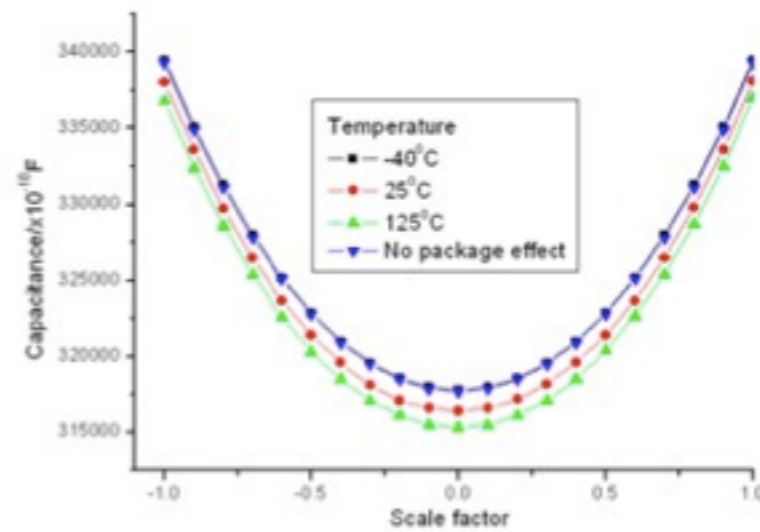
# Mode Matched Tuning Fork Gyro (M<sup>2</sup>-TFG)



# Mode Matched Tuning Fork Gyro (M<sup>2</sup>-TFG)

Table 2 Strain energy (×1e-12 J) vs. scale factor of mode 1

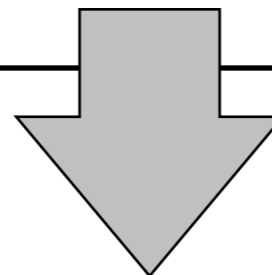
Scale factor	-40°C	25°C	125°C	No packaging effects
-1	51544.9	32544.9	12941.8	47.9935
-0.9	51535.7	32535.7	12932.8	38.7439
-0.8	51527.5	32527.5	12924.9	30.52
-0.7	51520.3	32520.3	12917.9	23.3043
-0.6	51514.1	32514.1	12911.9	17.0817
-0.5	51508.9	32508.9	12906.8	11.839
-0.4	51504.6	32504.6	12902.7	7.5647
-0.3	51501.3	32501.3	12899.5	4.24984
-0.2	51498.9	32498.9	12897.2	1.88715
-0.1	51497.5	32497.5	12895.8	0.471517
0	51497	32497	12895.4	5.22E-07
0.1	51497.5	32497.5	12895.8	0.471503
0.2	51498.9	32498.9	12897.2	1.88711
0.3	51501.3	32501.3	12899.5	4.24983



**Strain Energy  
(Look Up Table)**

**Electrostatic energy**

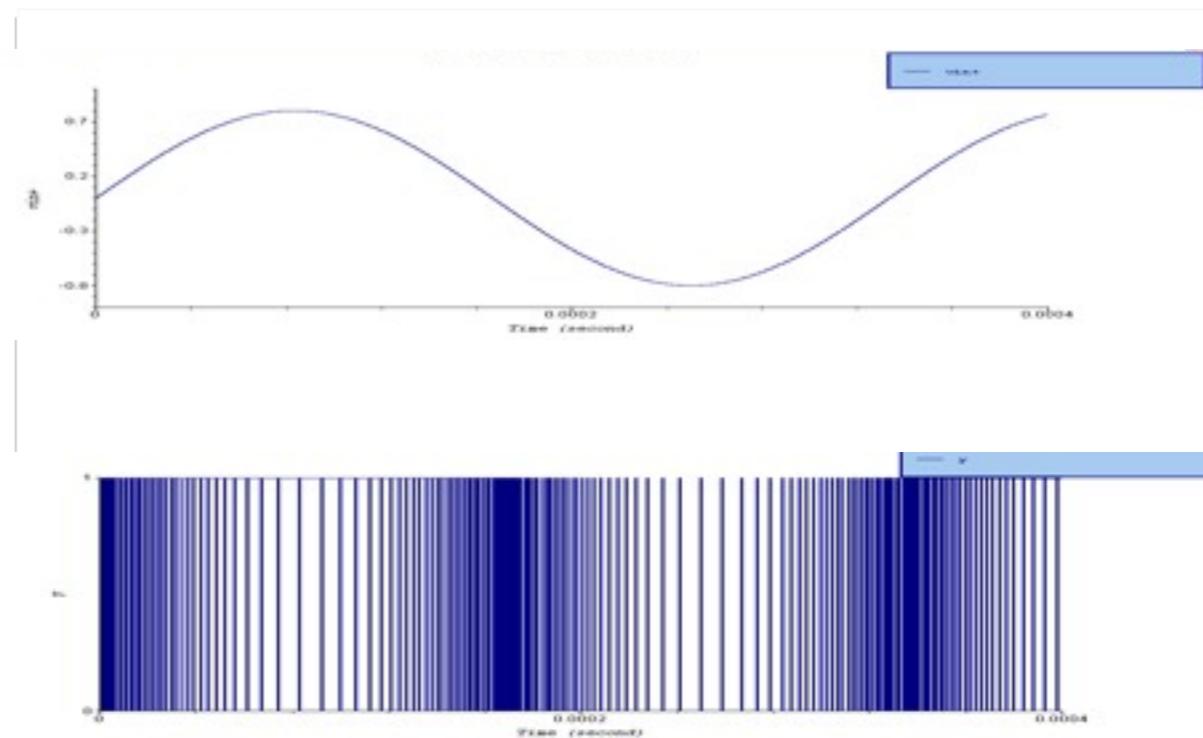
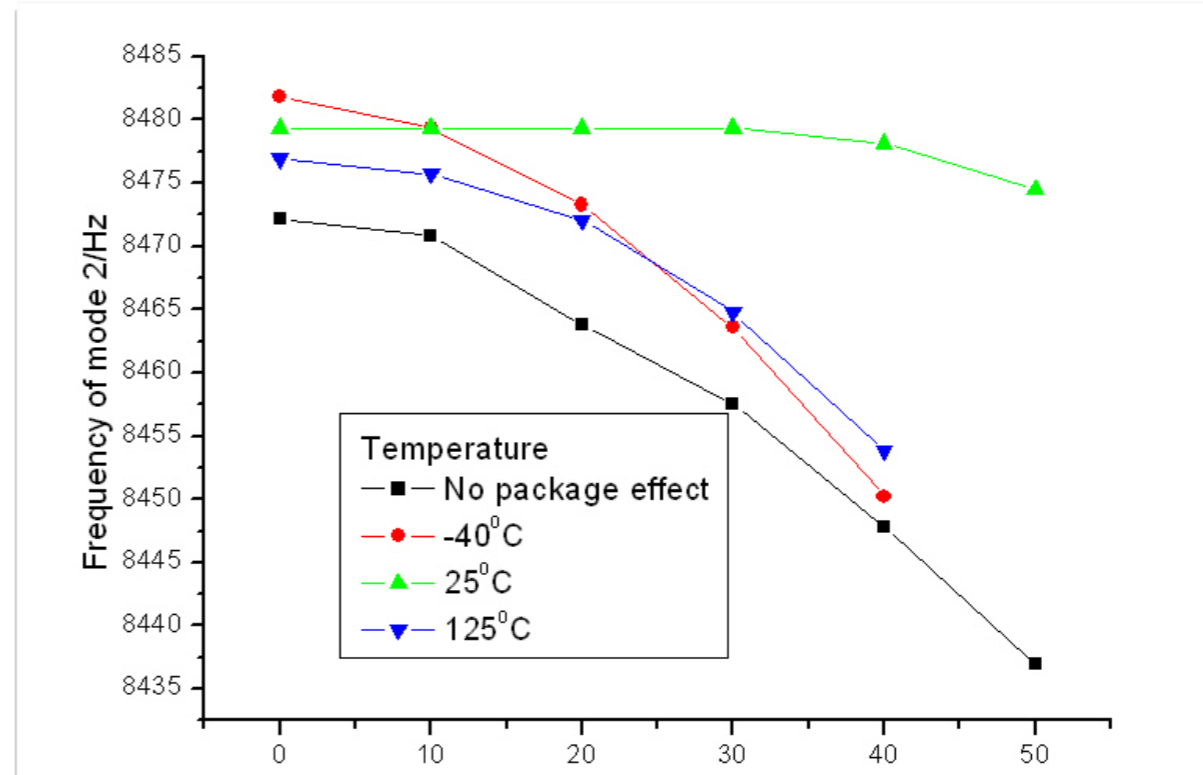
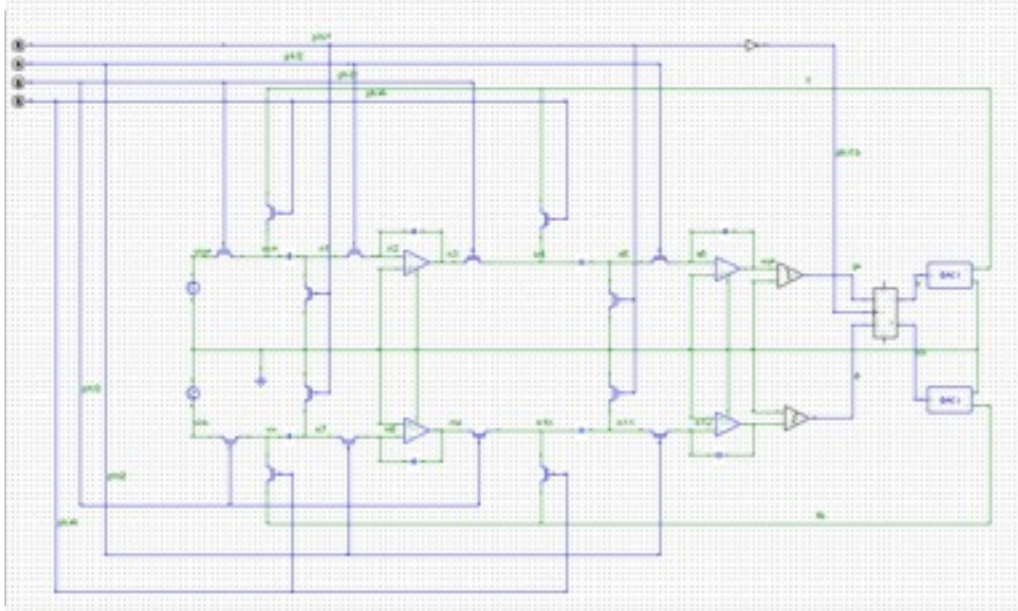
**Fluid damping characteristics**



**HDL Model**

**Cadence, Synopsys, Mentor, Mathworks  
(Spectre, HSPICE, Eldo, Simulink, System Vision...)**

# Verilog-A modeling results...



# Summary

- ▶ New packaging approaches represent an opportunity to rethink MEMS platforms
- ▶ MEMS increasingly is subsuming the package
- ▶ MEMS Design Is a collaboration challenge
- ▶ New generation EDA tools aimed at breaking 'chain of pain'
  - ▶ Allow seamless integration of WLP MEMS+ASIC